



Unlocking the Efficiency Potential of Perovskite Solar Cells: from Single-junction to Tandem

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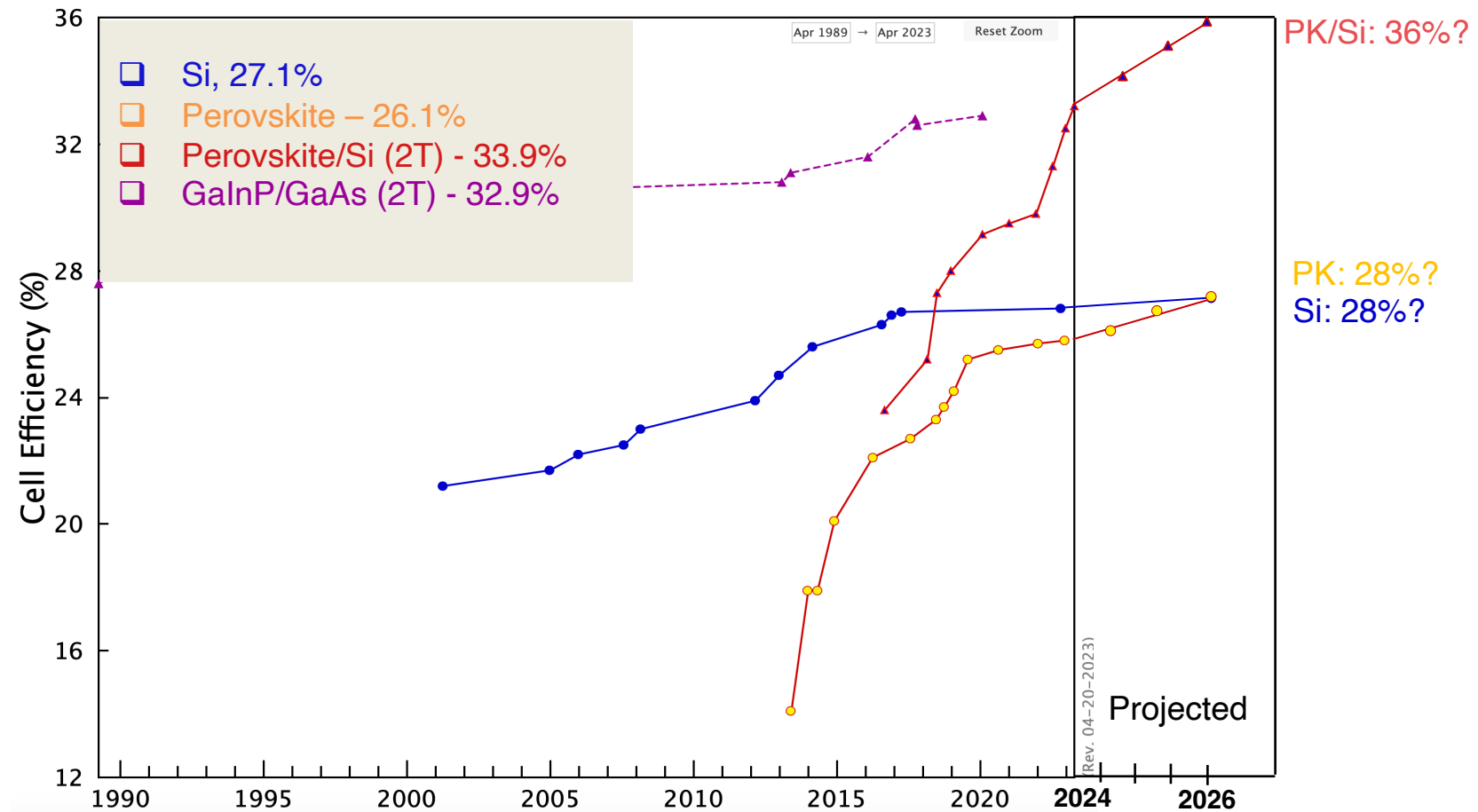
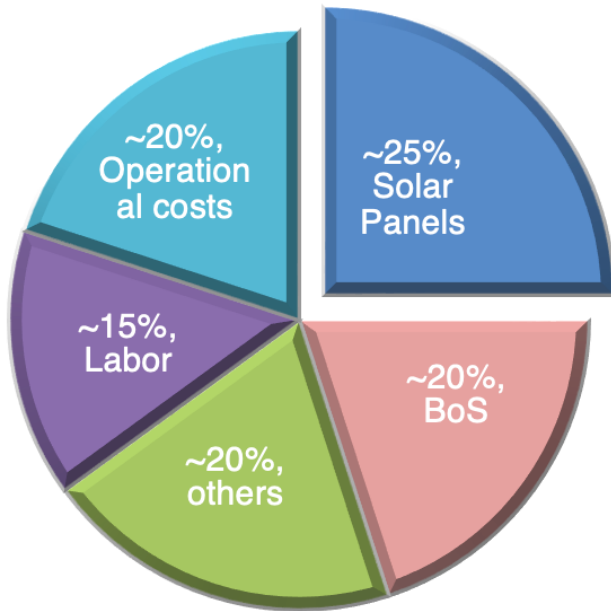
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PV panel cost accounts for a small fraction of system

Solar cell system cost breakdown



- Single-junction perovskite exceeds the efficiency of silicon?
- Where is the limit of perovskite-based MJ?

PV Records (cell area >1 cm²)

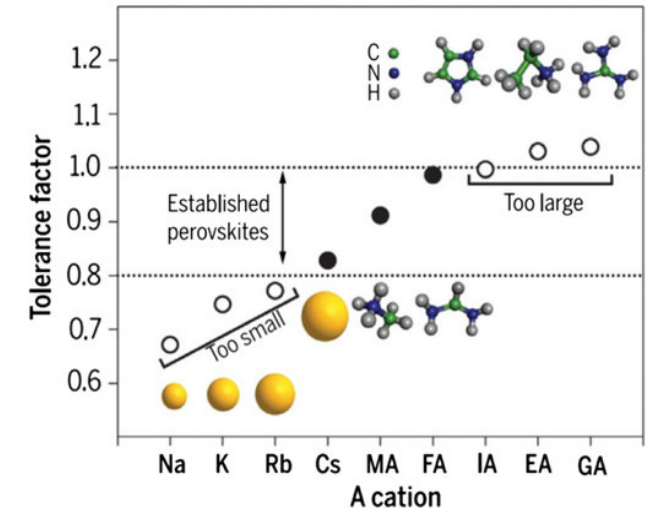
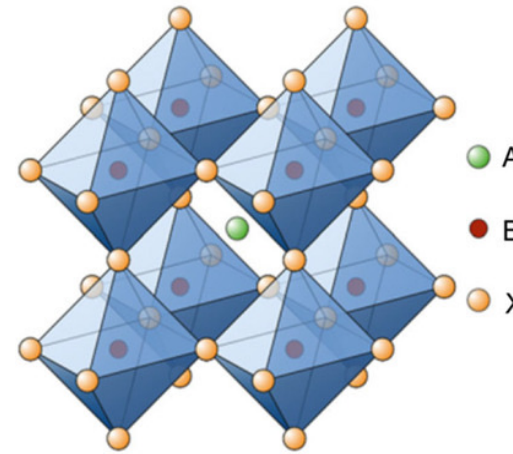
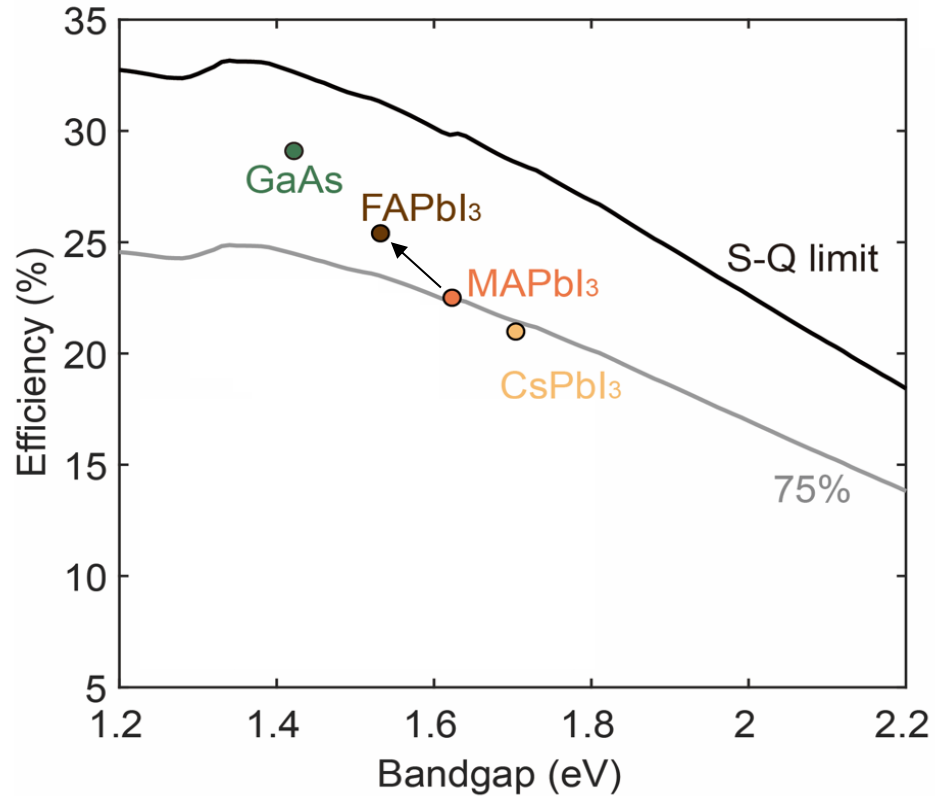
- ❑ Perovskite has outperformed most thin-film PV technologies
- ❑ Reducing the PCE disparity with GaAs (1.4eV) and Si (1.1eV) by optimizing bandgaps

Thin-film-based PV technologies

TABLE 1 Confirmed single-junction terrestrial cell and submodule efficiencies measured under the global AM1.5 spectrum (1000 W/m²) at 25°C (IEC 60904-3: 2008 or ASTM G-173-03 global).

Classification	Efficiency (%)	Area (cm ²)	V _{oc} (V)	J _{sc} (mA/cm ²)	Fill factor (%)	Test centre (date)	Description
Silicon							
Si (crystalline cell)	26.8 ± 0.4 ^a	274.4 (t)	0.7514	41.45 ^b	86.1	ISFH (10/22)	LONGi, n-type HJT ⁴
Si (DS wafer cell)	24.4 ± 0.3 ^a	267.5 (t)	0.7132	41.47 ^c	82.5	ISFH (8/20)	Jinko Solar, n-type
Si (thin transfer submodule)	21.2 ± 0.4	239.7 (ap)	0.687 ^e	38.50 ^{d,e}	80.3	NREL (4/14)	Solexel (35 μm thick) ⁵
Si (thin-film minimodule)	10.5 ± 0.3	94.0 (ap)	0.492 ^e	29.7 ^{d,f}	72.1	FhG-ISE (8/07)	CSG Solar (<2 μm on glass) ⁶
III-V cells							
GaAs (thin-film cell)	29.1 ± 0.6	0.998 (ap)	1.1272	29.78 ^g	86.7	FhG-ISE (10/18)	Alta Devices ⁷
GaAs (multicrystalline)	18.4 ± 0.5	4.011 (t)	0.994	23.2	79.7	NREL (11/95)	RTI, Ge substrate ⁸
InP (crystalline cell)	24.2 ± 0.5 ^h	1.008 (ap)	0.939	31.15 ⁱ	82.6	NREL (3/13)	NREL ⁹
Thin-film chalcogenide							
CIGS (cell) (Cd-free)	23.35 ± 0.5	1.043 (da)	0.734	39.58 ^j	80.4	AIST (11/18)	Solar Frontier ¹⁰
CIGSSe (submodule)	20.3 ± 0.4	526.7 (ap)	0.6834	39.55 ^{dk}	75.1	NREL (5/23)	Avancis, 100 cells ¹¹
CdTe (cell)	21.0 ± 0.4	1.0623 (ap)	0.8759	30.25 ^e	79.4	Newport (8/14)	First Solar, on glass ¹²
CZTSSe (cell)	12.1 ± 0.3	1.066 (da)	0.5379	35.29 ^k	63.6	NPVM (4/23)	IoP/CAS ¹³
CZTS (cell)	10.0 ± 0.2	1.113 (da)	0.7083	21.77 ⁱ	65.1	NREL (3/17)	UNSW ¹⁴
Amorphous/microcrystalline							
Si (amorphous cell)	10.2 ± 0.3 ^{L,h}	1.001 (da)	0.896	16.36 ^e	69.8	AIST (7/14)	AIST ¹⁵
Si (microcrystalline cell)	11.9 ± 0.3 ^h	1.044 (da)	0.550	29.72 ⁱ	75.0	AIST (2/17)	AIST ¹⁶
Perovskite							
Perovskite (cell)	24.35 ± 0.5 ^m	1.007 (da)	1.159	25.60 ^k	82.1	NPVM (4/23)	NUS/SERIS ¹⁷
Perovskite (minimodule)	22.4 ± 0.5 ^m	26.02 (da)	1.127 ^d	25.61 ^{d,b}	77.6	NPVM (7/22)	EPFLSion/NCEPU, 8 cells ¹⁸

Approaching the ideal bandgap of GaAs

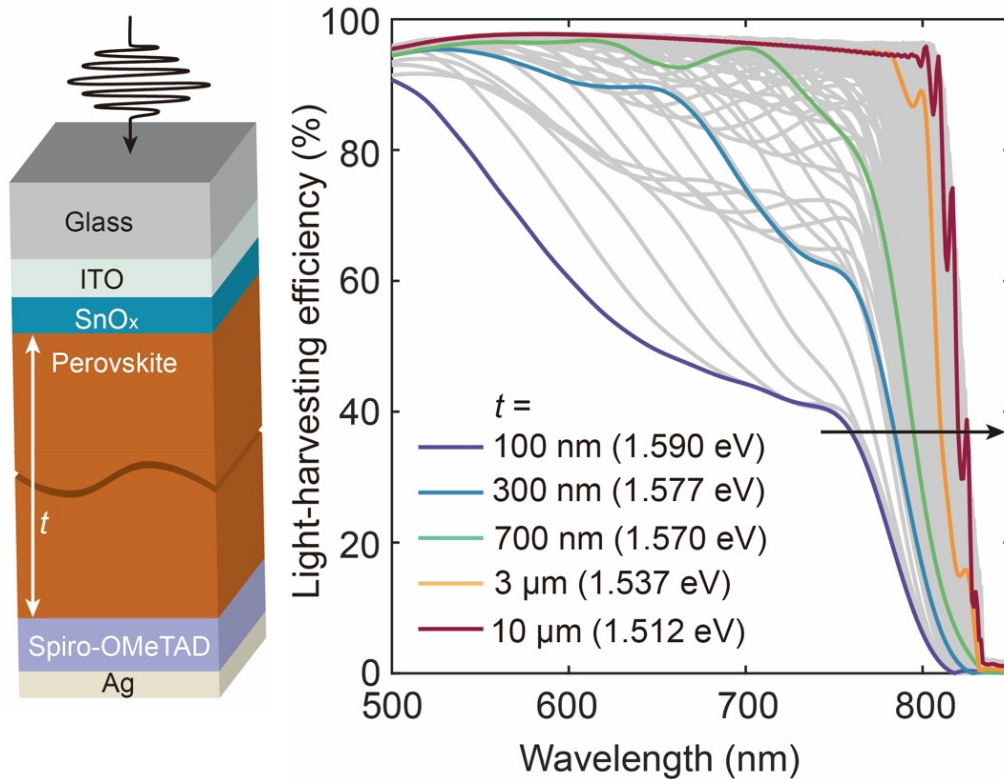


$$t = \frac{(r_A + r_X)}{\sqrt{2}(r_B + r_X)}$$

❑ Approaching the ideal bandgap of GaAs

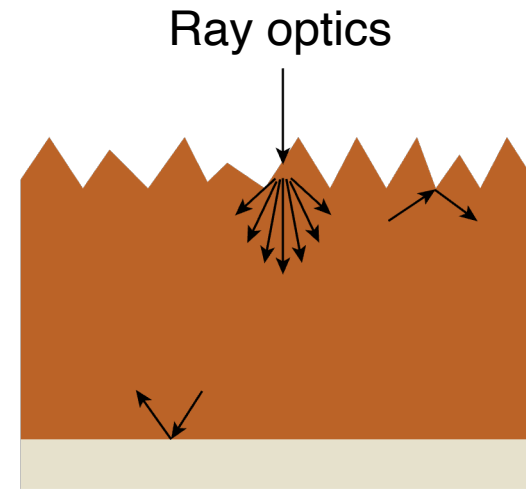
❑ Composition engineering has reached its inherent limits

Traditional light management based on ray optics



Yablonoitch limit = $4n^2$ fold

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Statistical ray optics

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Eli Yablonoitch

$n(\text{Si}): 3.7$
 $n(\text{GaAs}): 3.7$
 $n(\text{Perovskite}): 2.4$

❑ $> 10 \mu\text{m}$ -thick single crystal perovskite has a narrower PV bandgap

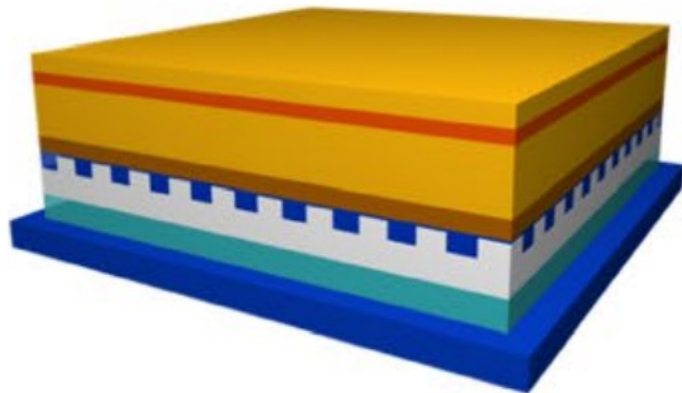
❑ Ray optics is not effective in extending perovskite band edge

Narrowing the PV bandgap of FAPbI₃

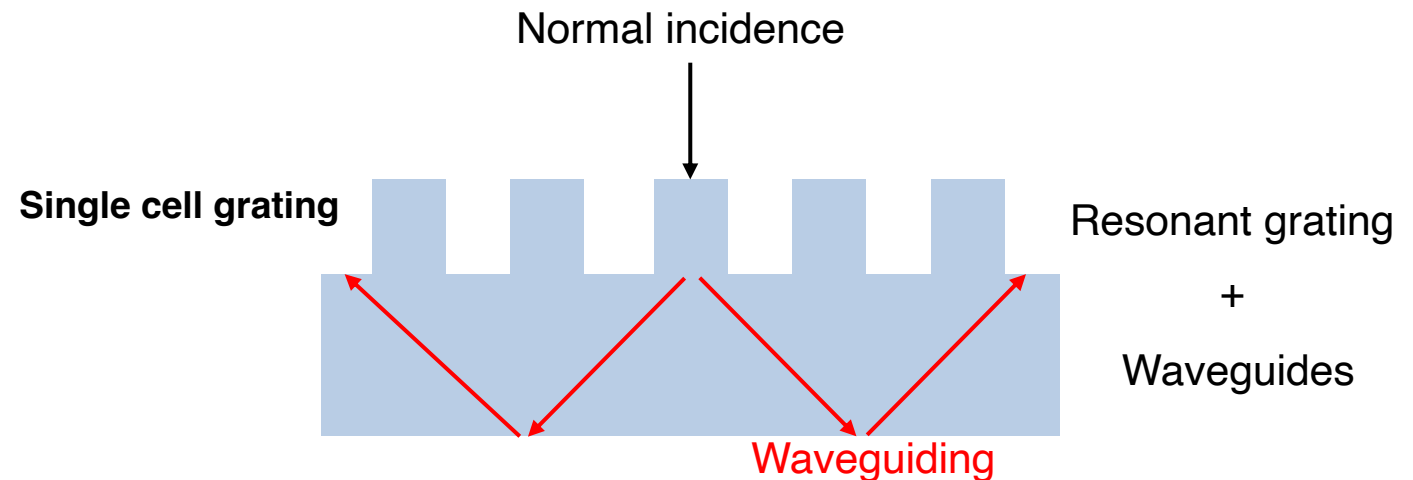
- *without composition engineering and increasing thickness*

Ultrathin GaAs solar cells (~200nm)

Wave optics
(single cell grating + high n)



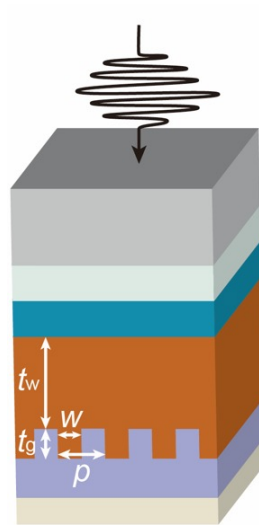
Nature Energy 4, 761-767 (2019)



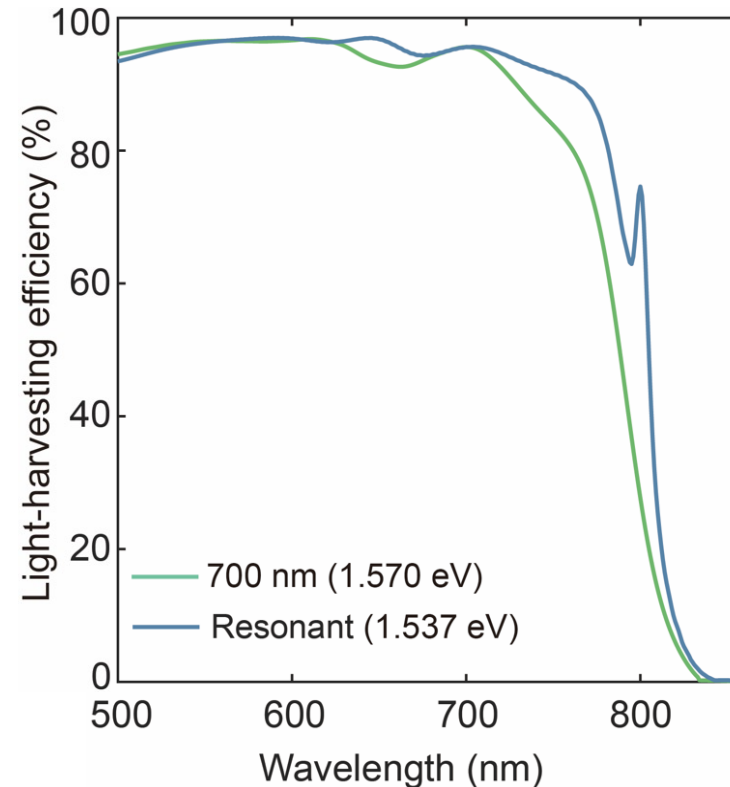
- Resonant grating for diffraction
- Strong light confinement and propagation in waveguides

Narrowing the PV bandgap of FAPbI_3

- without composition engineering and increasing thickness



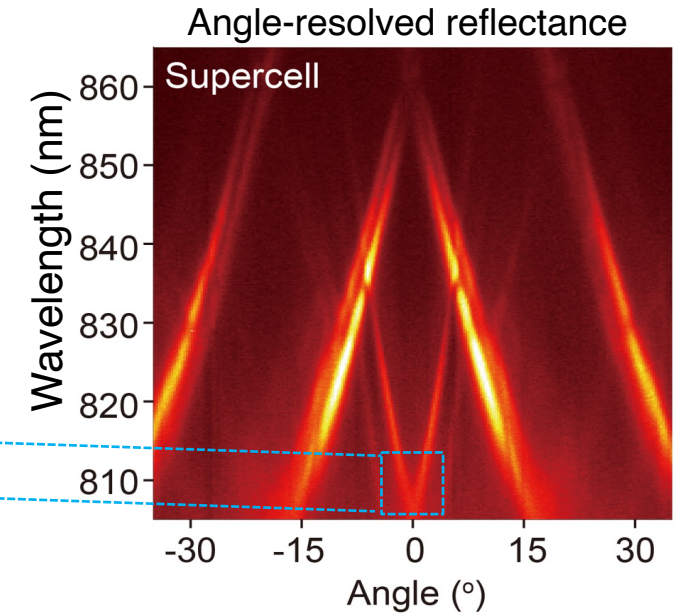
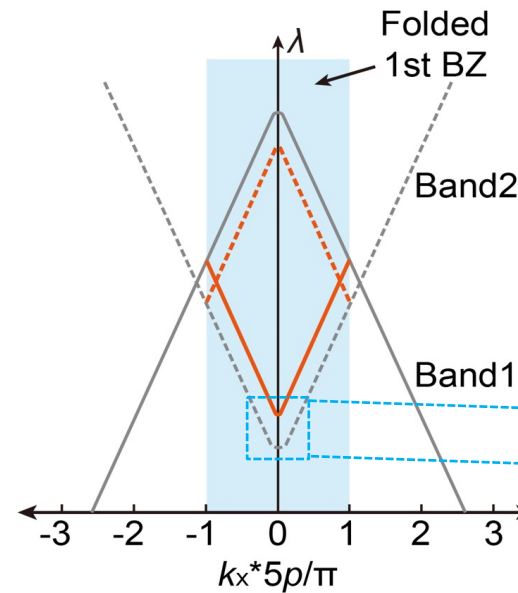
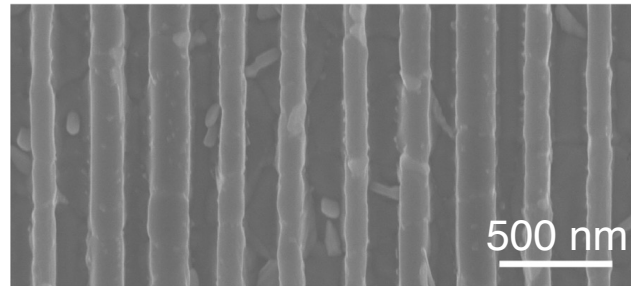
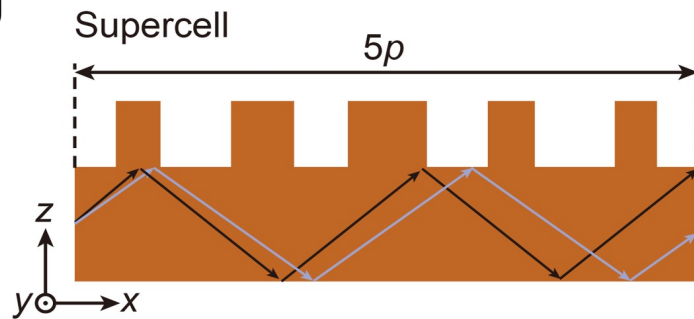
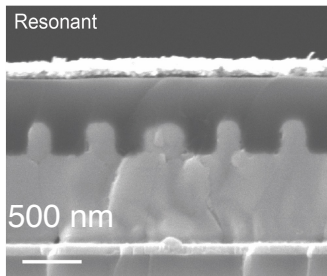
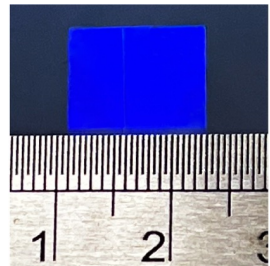
Resonant solar cells



- ❑ **Strong guided-mode resonances (GMRs)** couple normal incident light with waveguided modes
- ❑ GMRs significantly enhance light absorption even near band edge with **small absorption coefficients**

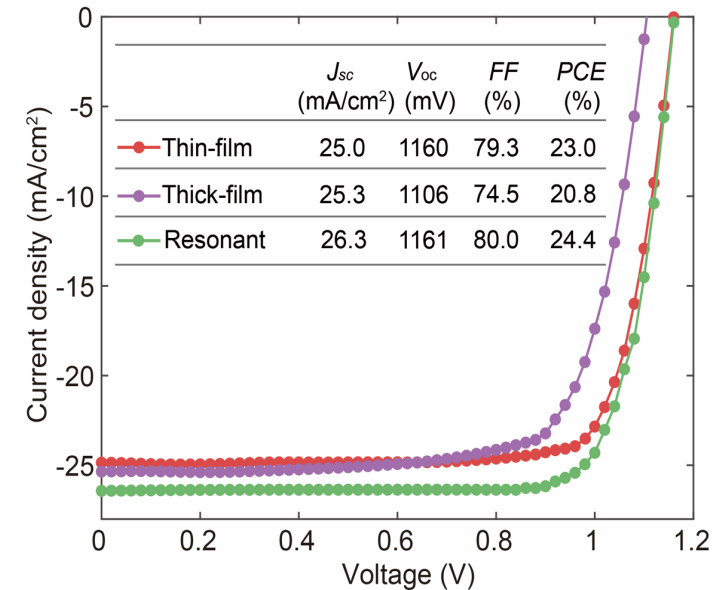
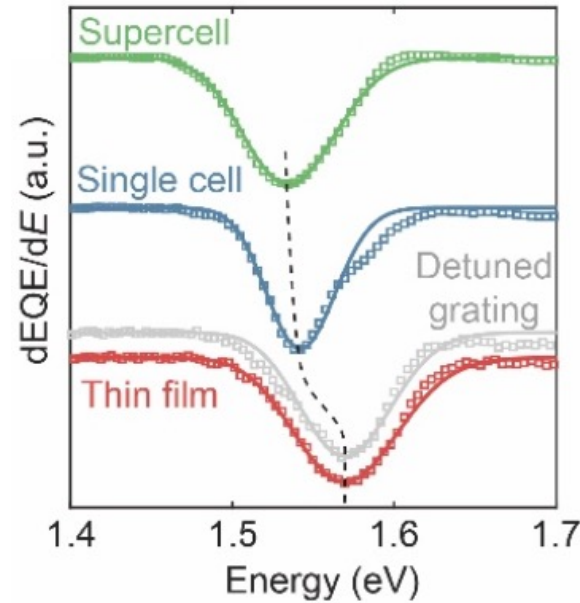
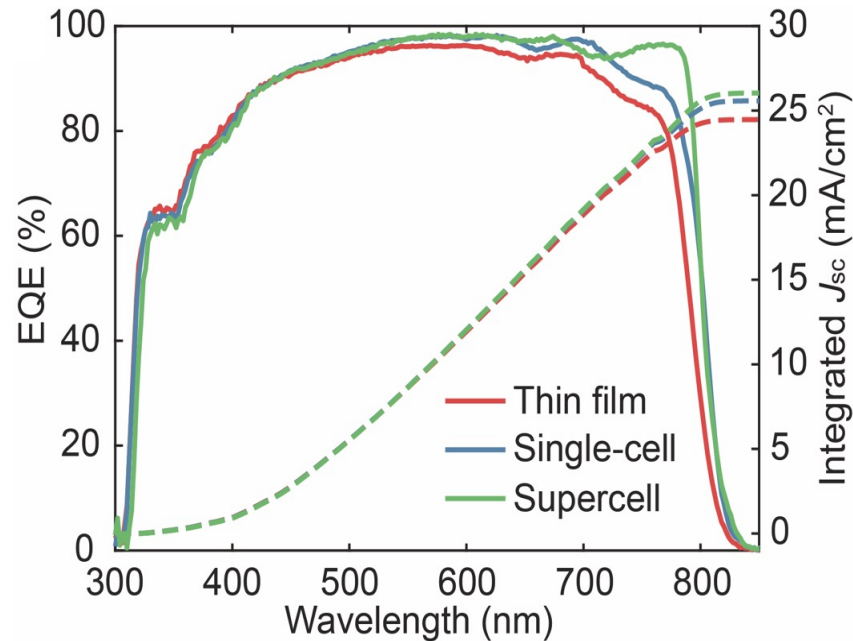
Resonant solar cells with Brillouin-zone folding

Nanoimprinting



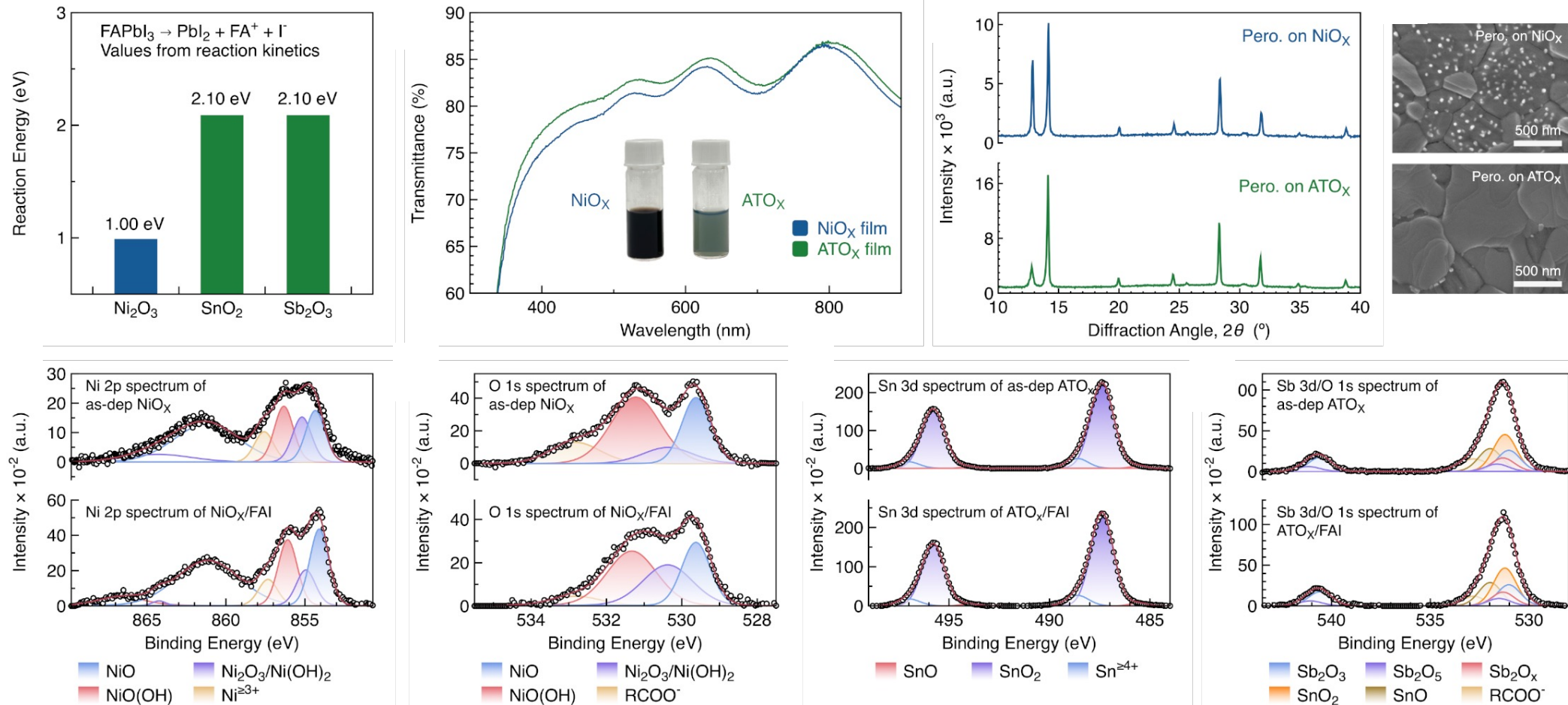
- ❑ Supercell can induce Brillouin-zone folding
- ❑ Brillouin-zone folding provides an approach to increase photonic density of states

Resonant solar cells with improved J_{sc}



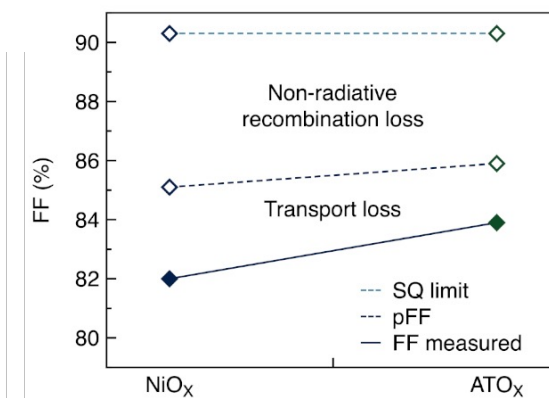
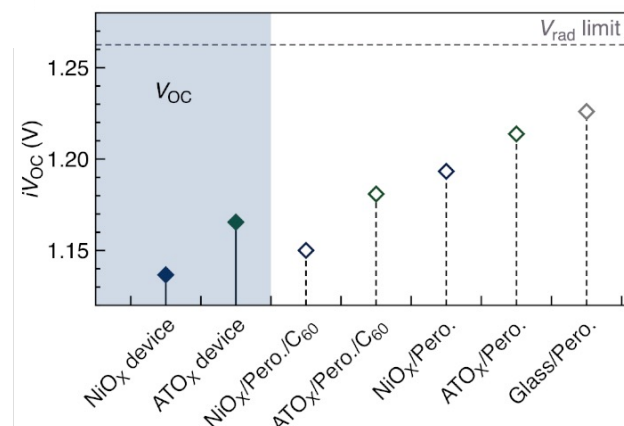
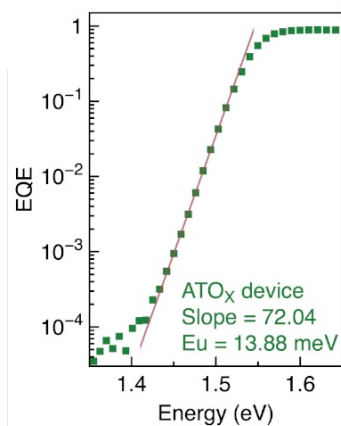
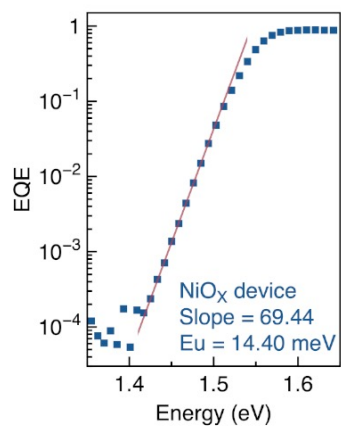
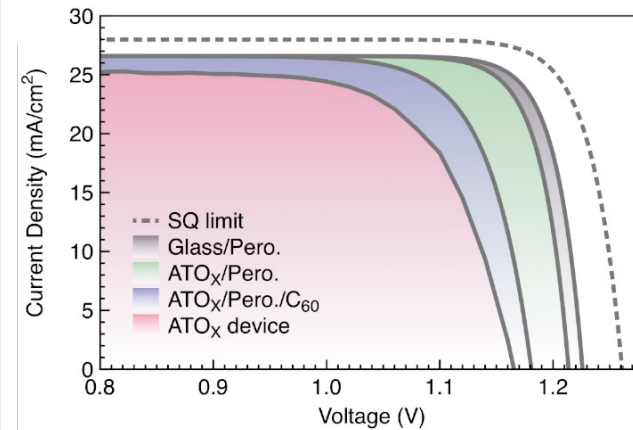
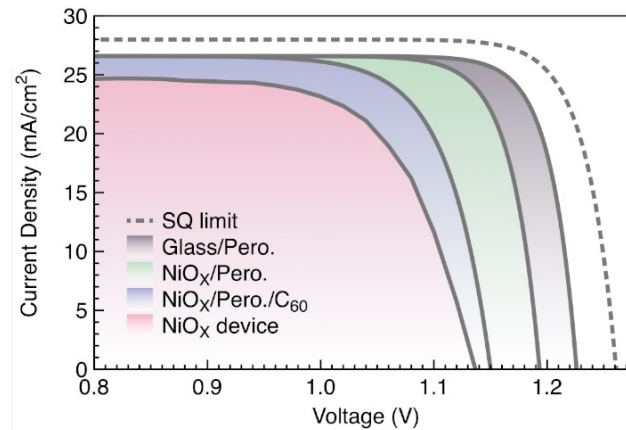
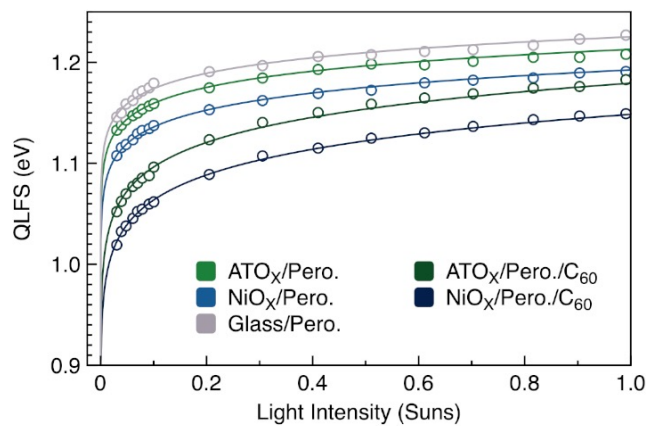
□ Resonant solar cells: 18 nm spectral extension, 35 meV band-edge extension, 1.5 mA/cm² J_{sc} improvement

Carrier management: Antimony doped tin oxides (ATOx) HTL



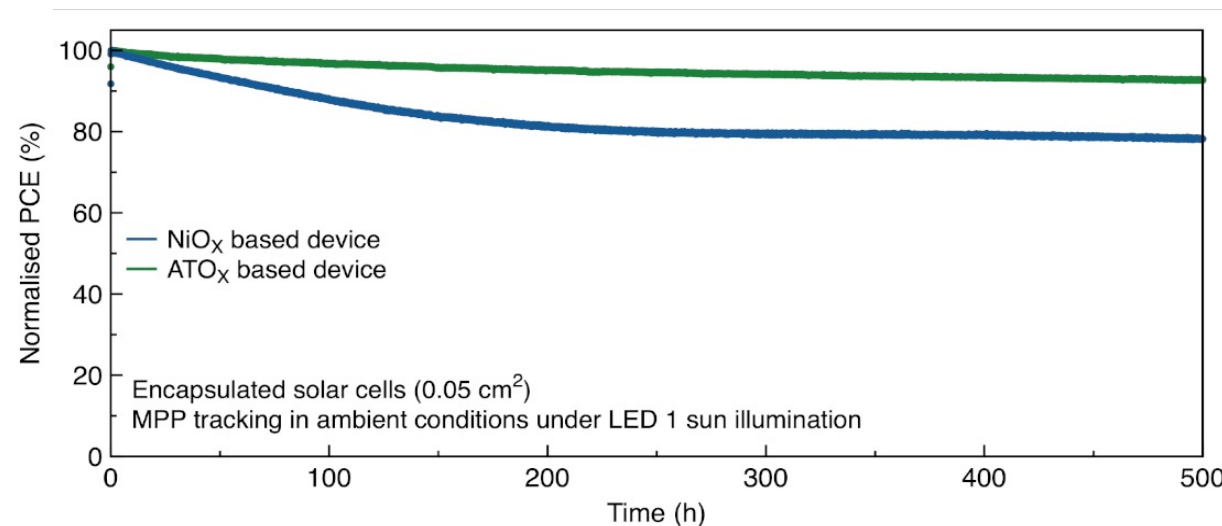
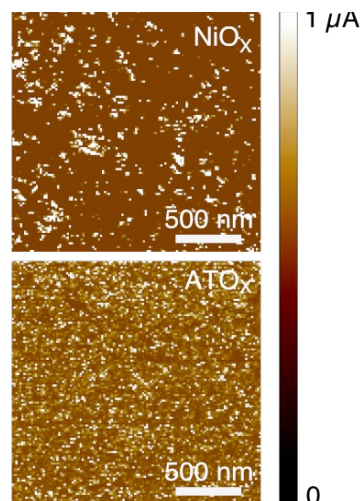
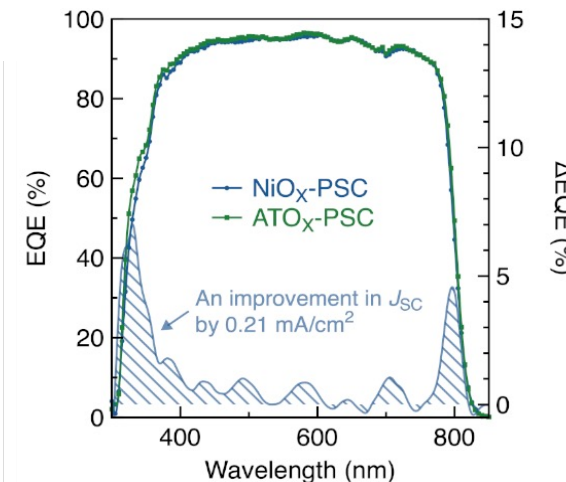
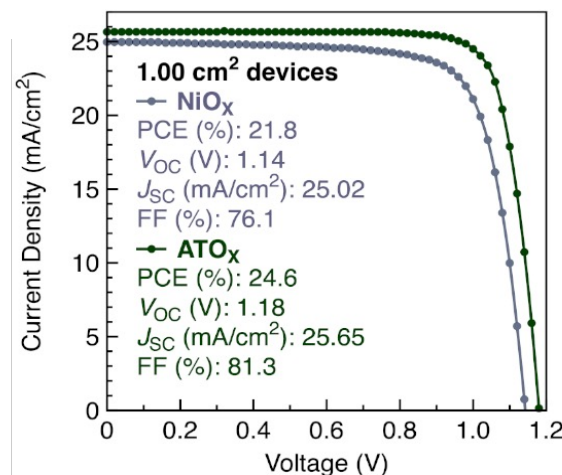
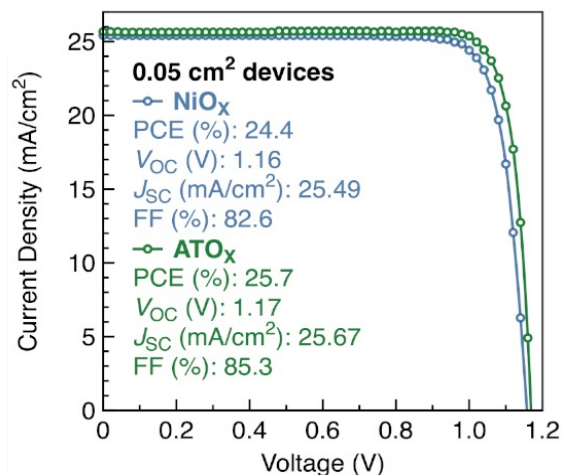
□ ATOx is a more stable and transparent HTL in “p-i-n” structured perovskite solar cell.

Voc improvement in ATOx cells



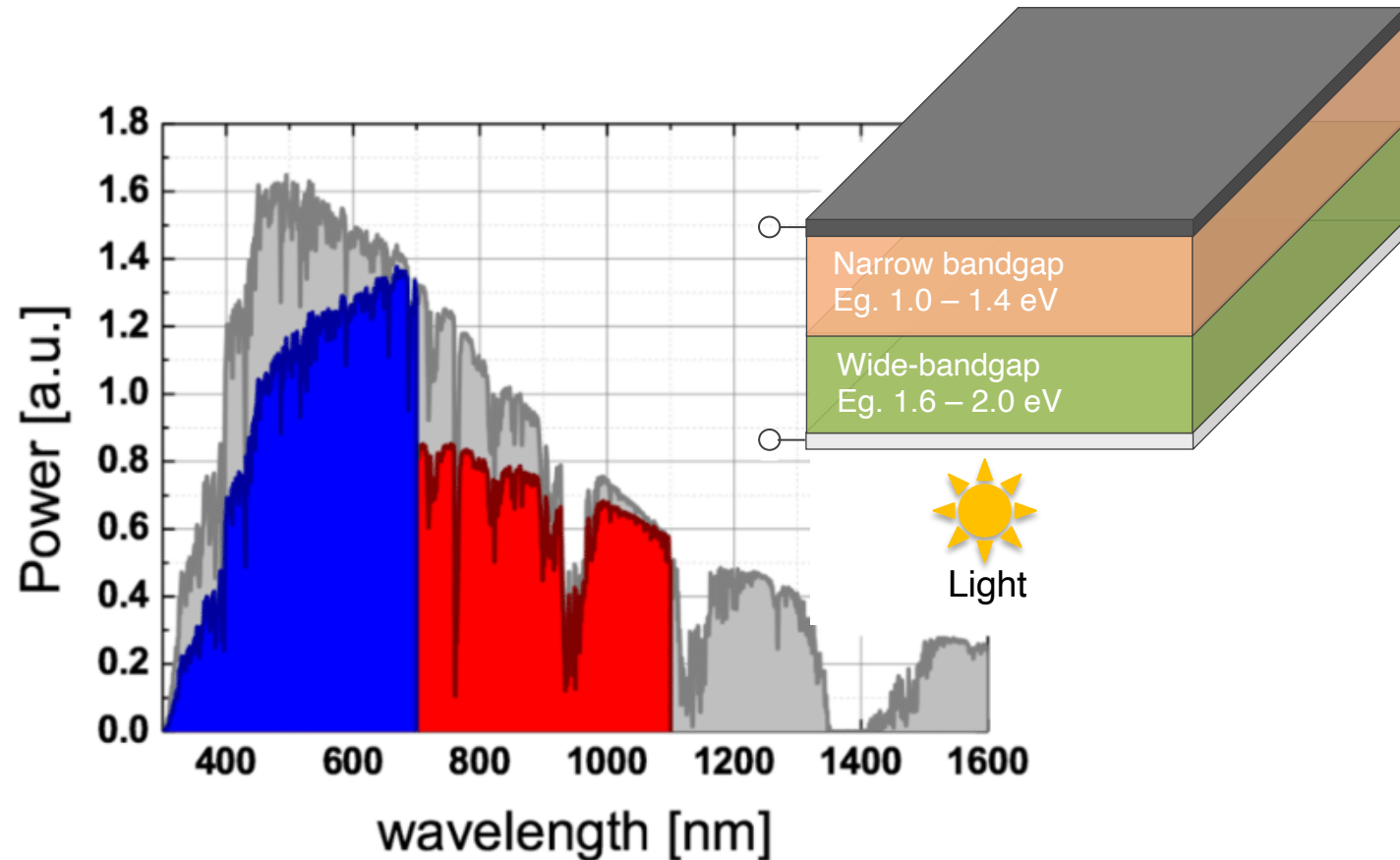
□ ATO_x suppresses non-radiative recombination in perovskites

Reduced PCE gap for cell sizes ranging from 0.05 to 1 cm²

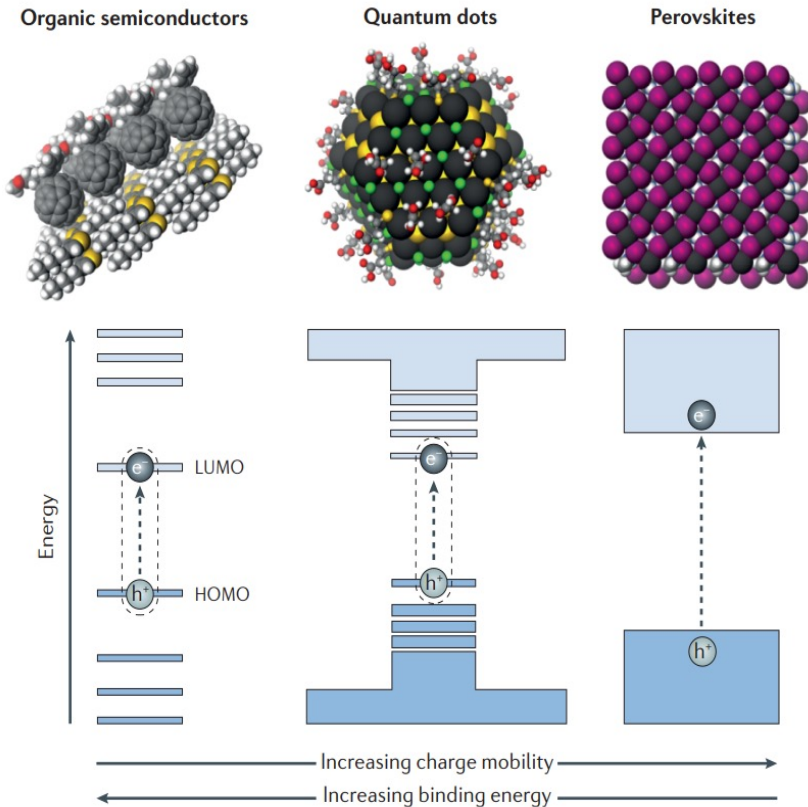


Tandem is one of the most practical solutions to overcome SQ limit

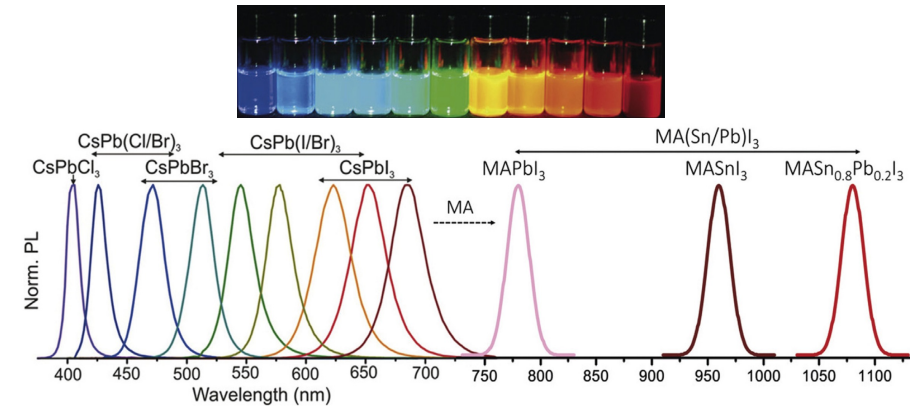
multiexciton generation
photon upconversion
tandem
hot carrier cell
intermediate band cell
photon downconversion



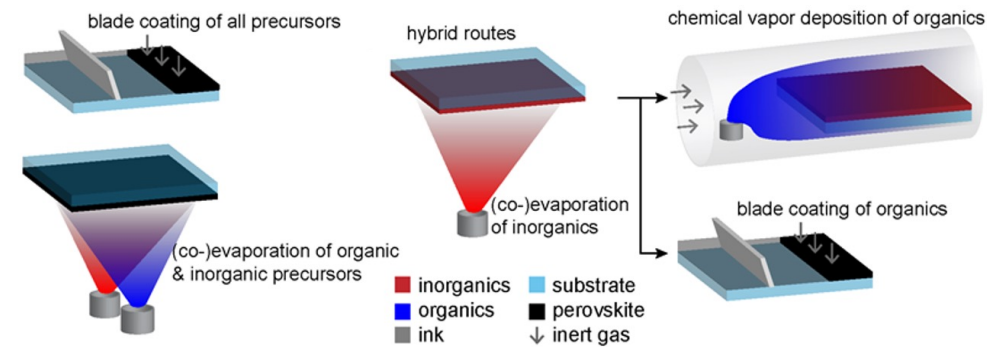
Perovskite – a fantastic wide-bandgap absorber



- Low exciton binding energy
- Long diffusion length
- Strong absorption

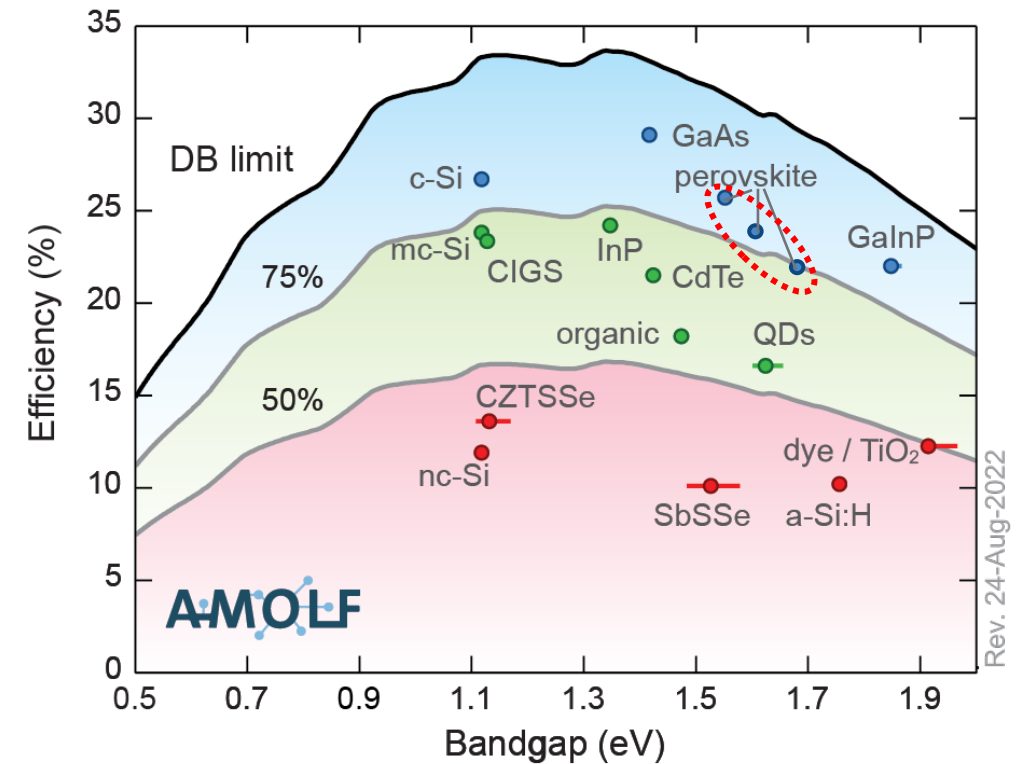
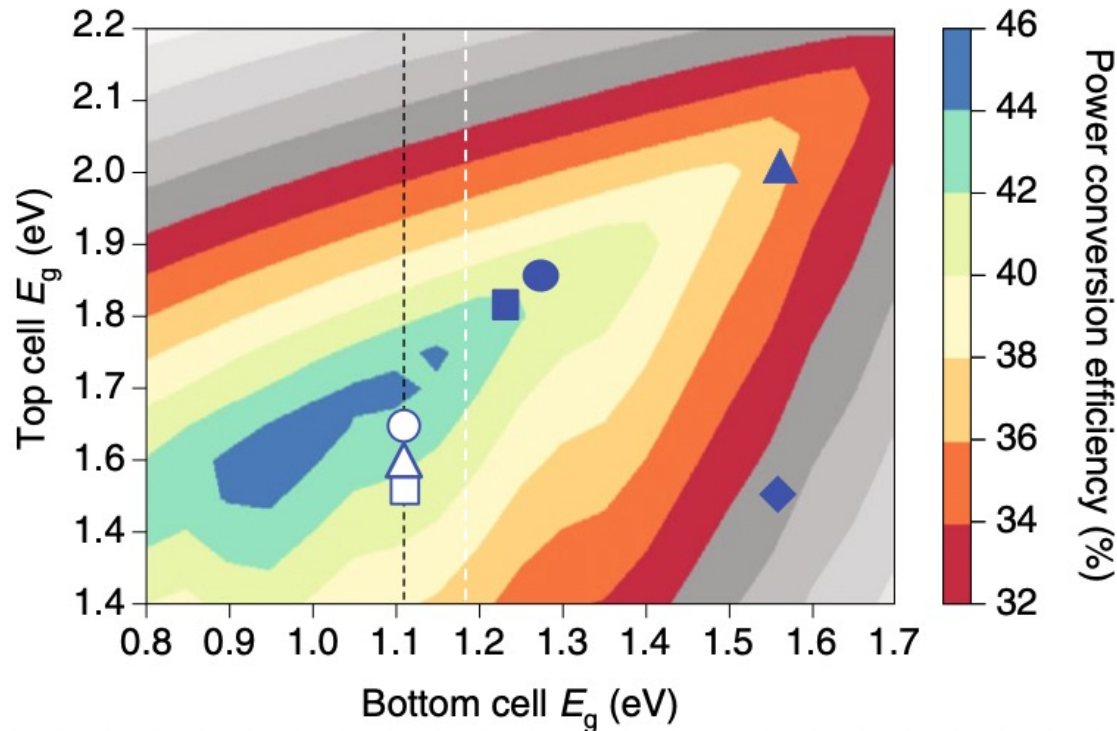


Bandgap tunability



Compatibility with vacuum and solution processing

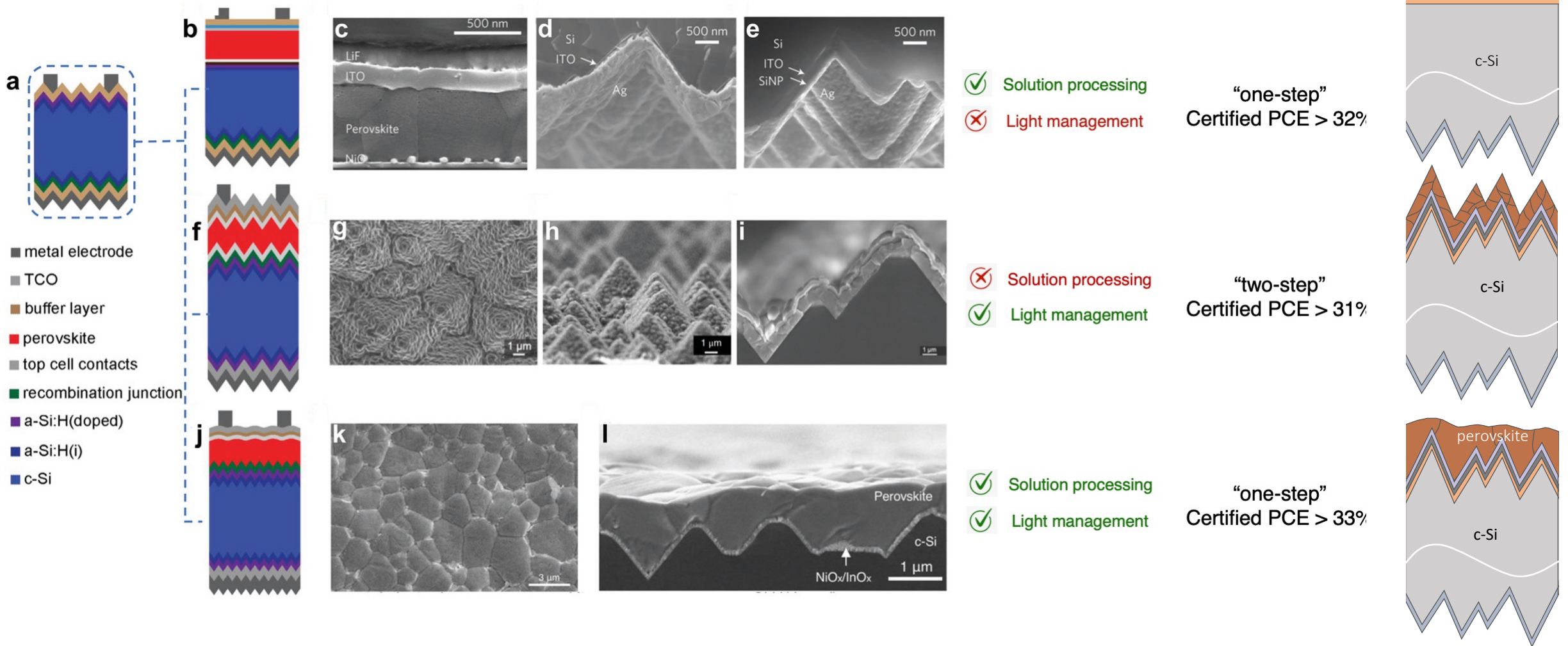
Perovskites - efficient wide-bandgap absorbers



□ Ideal tandem bandgaps: 1.0eV/1.6eV
e.g., Si requires perovskite Bandgap >1.65 eV

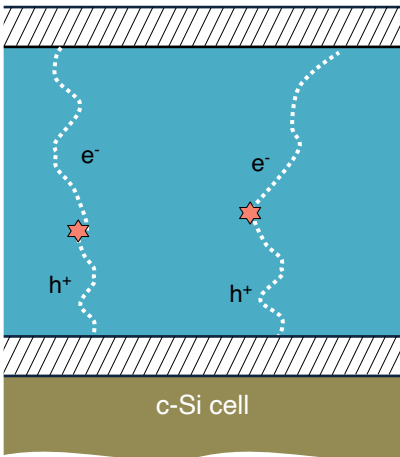
□ Efficient wide-bandgap absorbers

State-of-the art perovskite/Si tandem solar cell architecture evolution

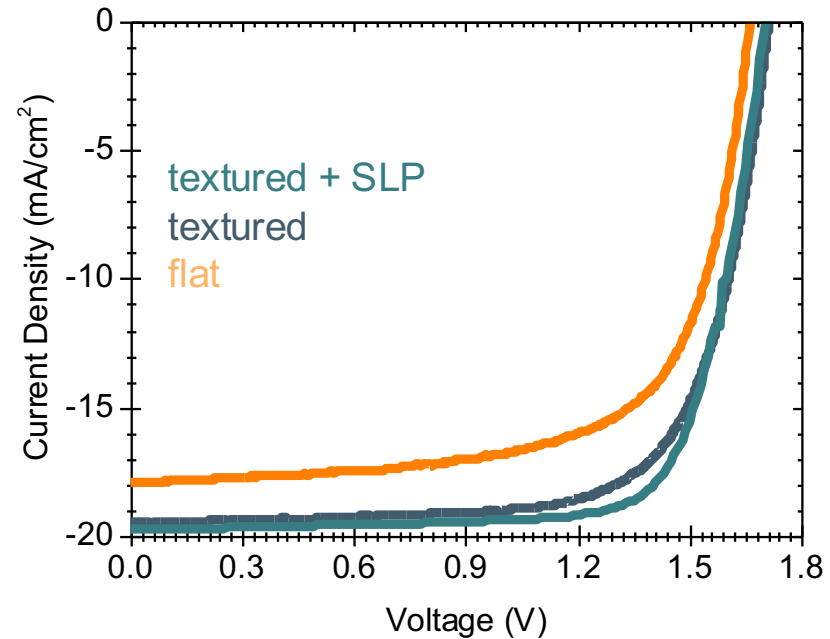
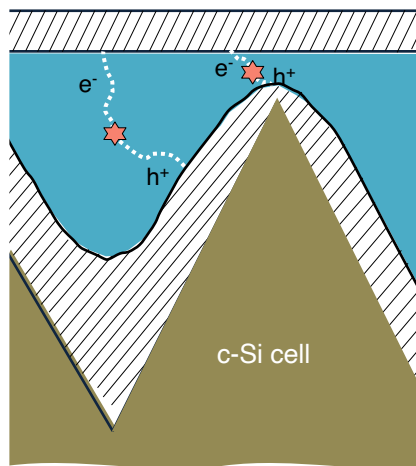





The depletion width correlates to the geometry factor

Flat cell



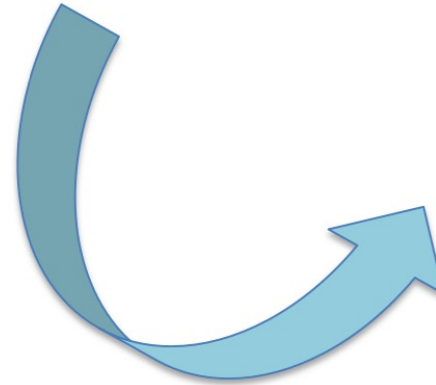
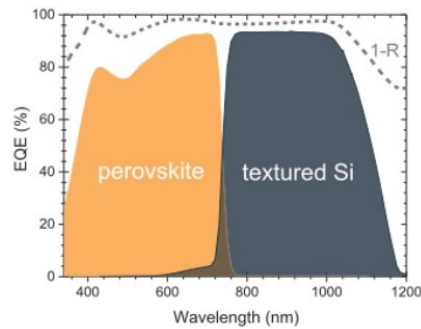
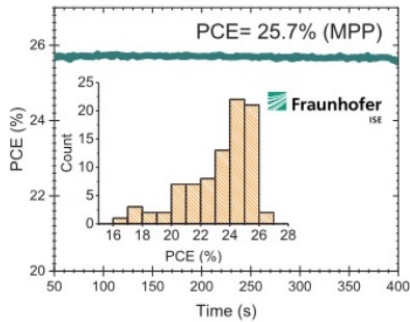
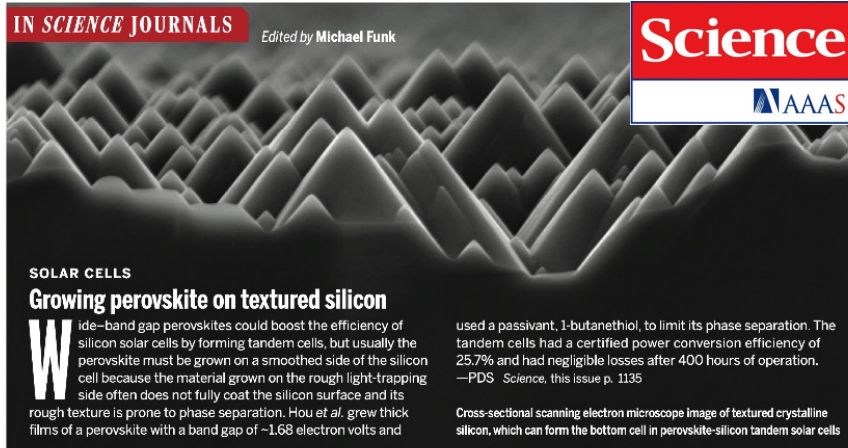
Textured cell



-  Drift dominant region in perovskite
-  Diffusion dominant region in perovskite
-  Charge generation region

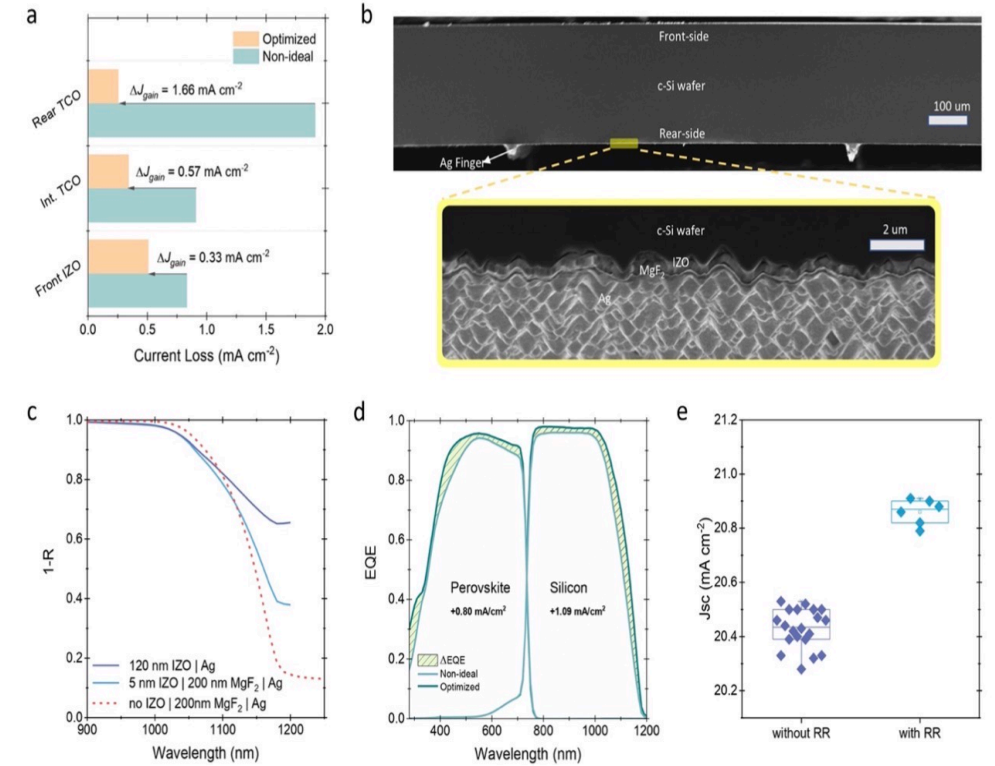
- Reduce carrier collection paths;
- Enhanced wetting of perovskite precursor;

Perovskite/Si tandem performances evolution



Hou, Y.; Aydin, E.; De Wolf, S.; Sargent, E. et al
Science, 367, 1135-1140 (2020)

Aydin, E.; Wolf, S. D. *et al.*
Nature, DOI: 10.1038/s41586-023-06667-4 (2023)



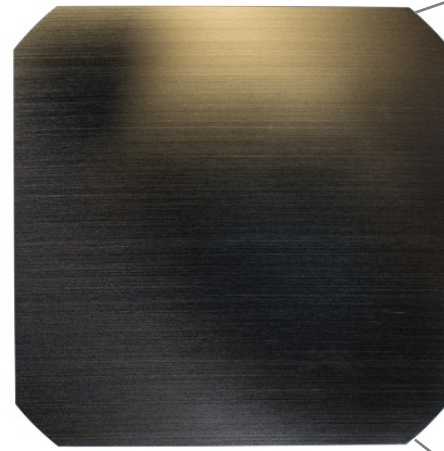
PCEs boost from 26% to 33%

Challenges in integrating perovskite with Cz-Si thin wafers

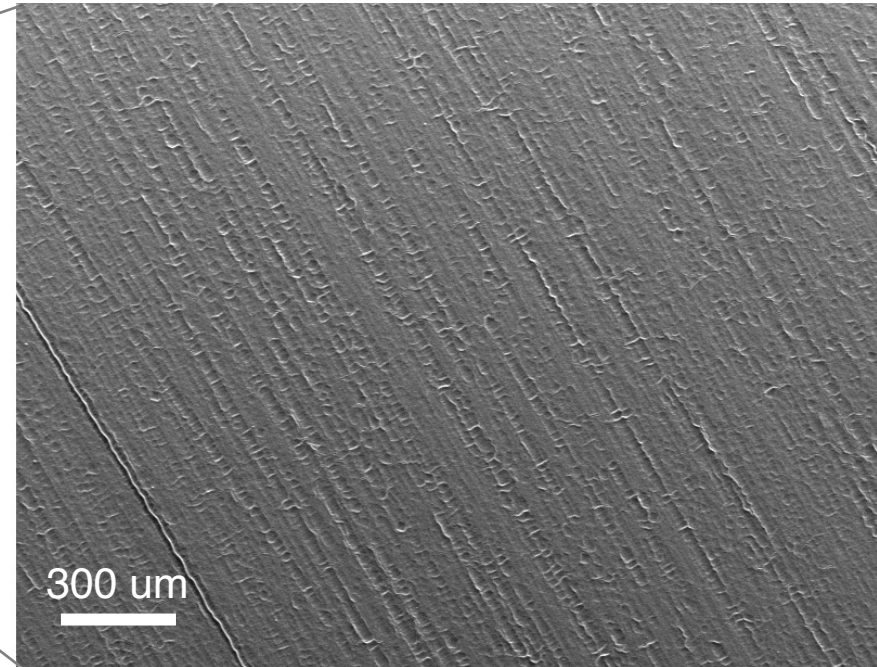
1. Saw marks on Si surface



Float Zone (FZ)
Price: > 60 USD/piece

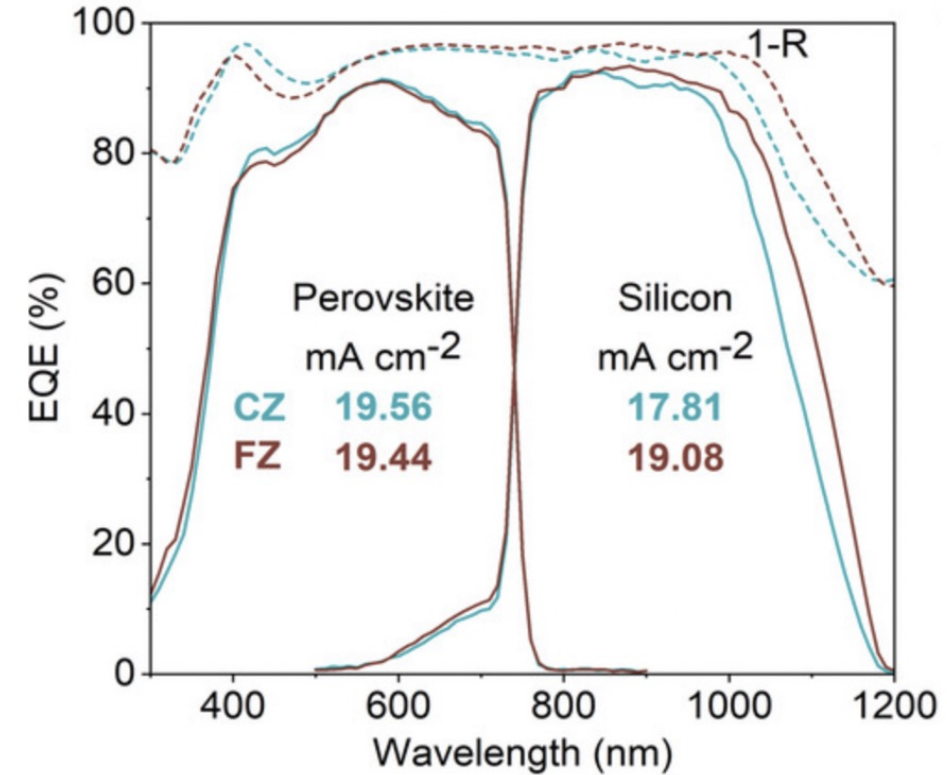
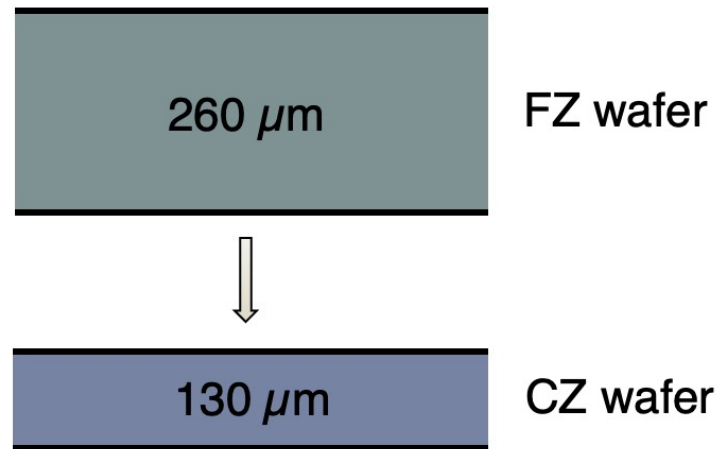


Czochralski (CZ)
Price: < 1 USD/piece

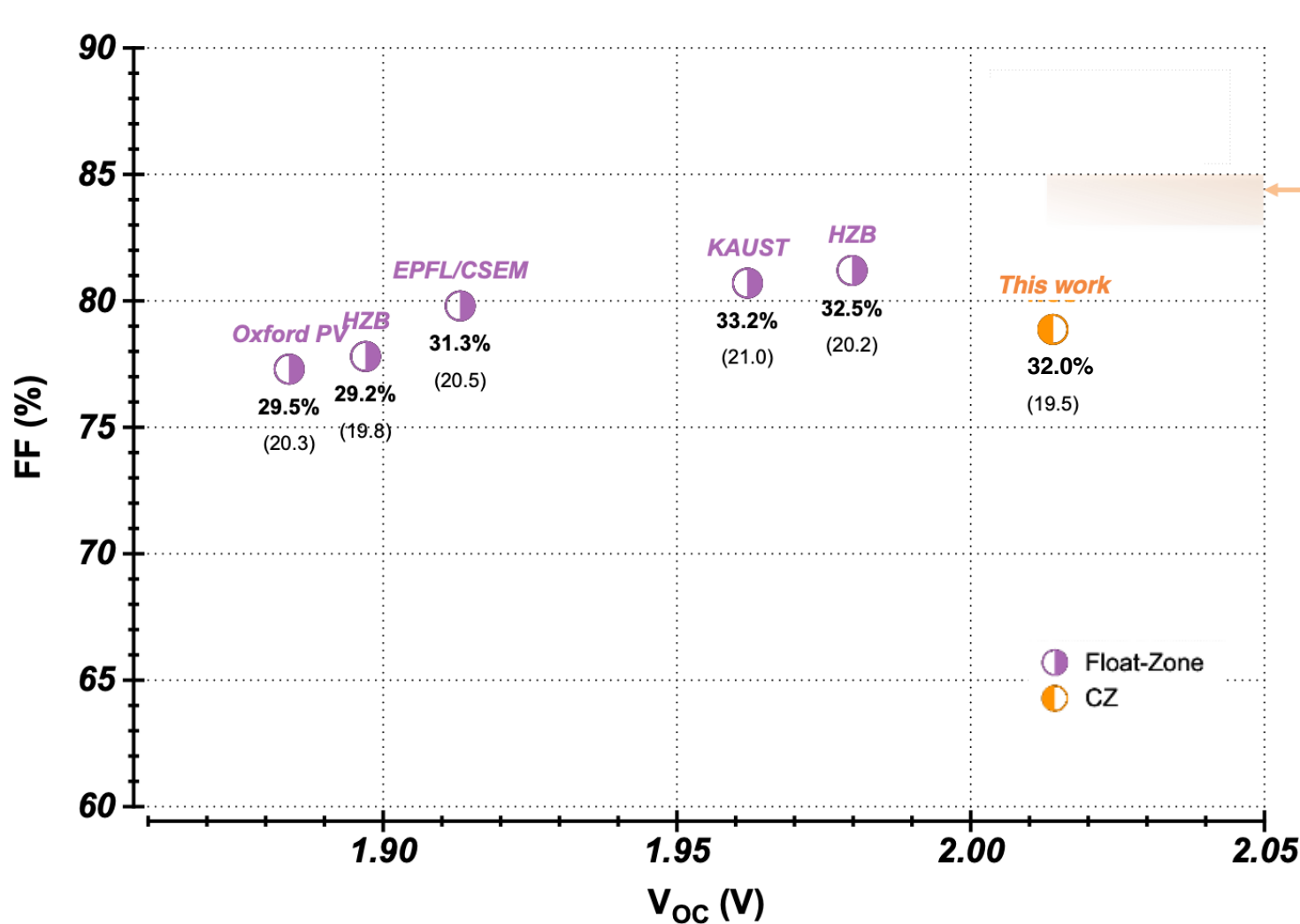


Challenges in integrating perovskite with Cz-Si thin wafers

2. Lower absorption at NIR



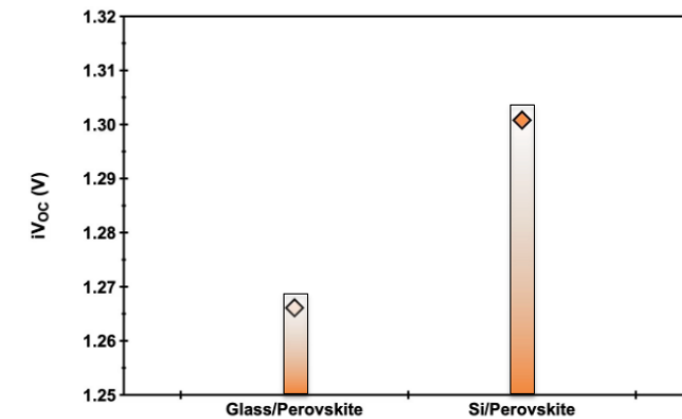
Where is the limit of perovskite/Si?



- Voc of perovskite: ~ 1.28 V
- Voc of shaded Si: ~ 0.72 V

Target zone

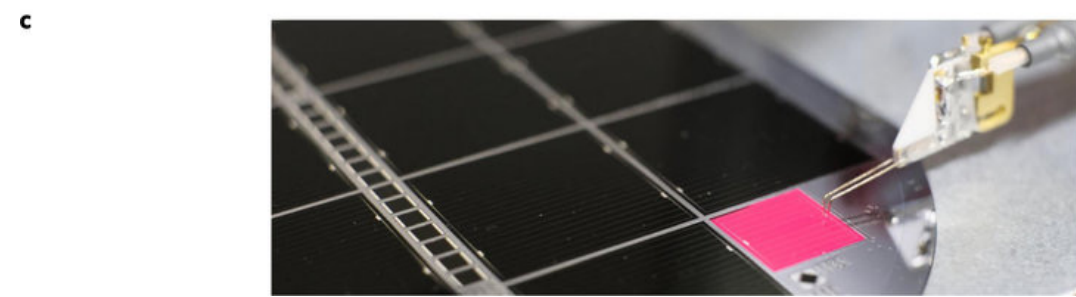
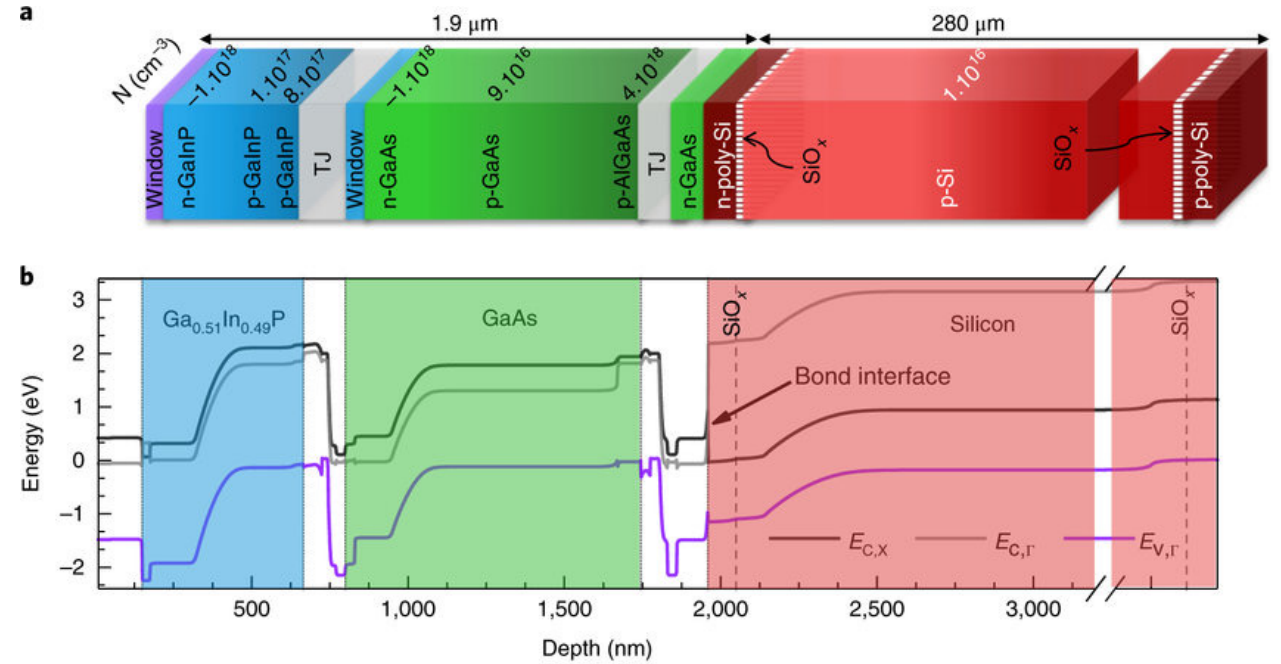
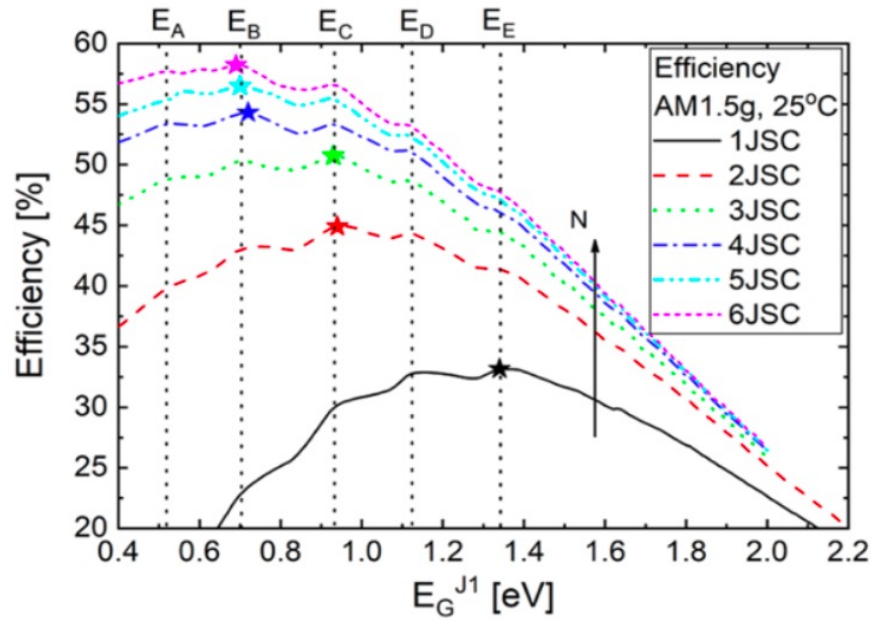
$iV_{oc} = 1.30V (1.70 eV)$



Achievable PCE:

$$2.05(V_{oc}) * 0.85(ff) * 21(J_{sc}) = 36.5\%(PCE)?$$

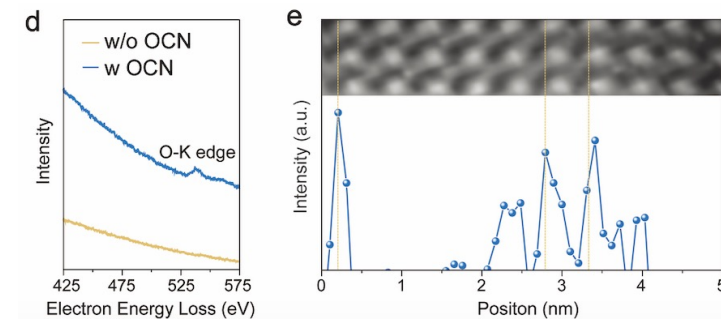
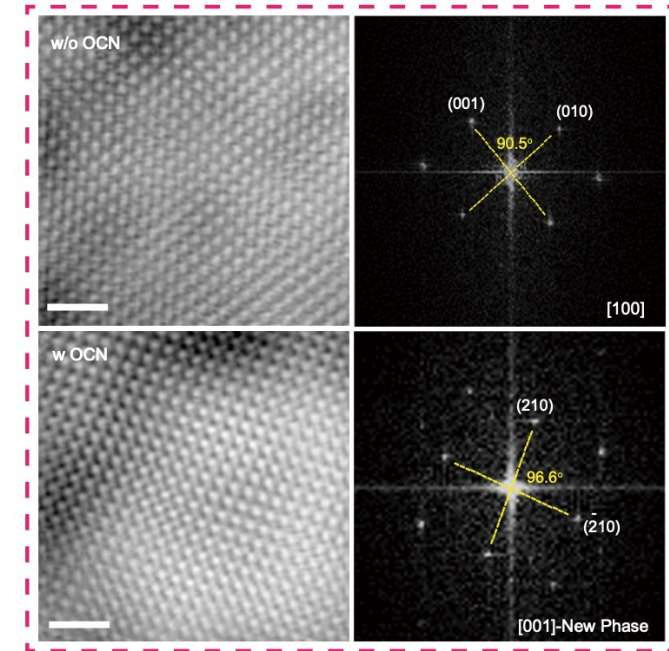
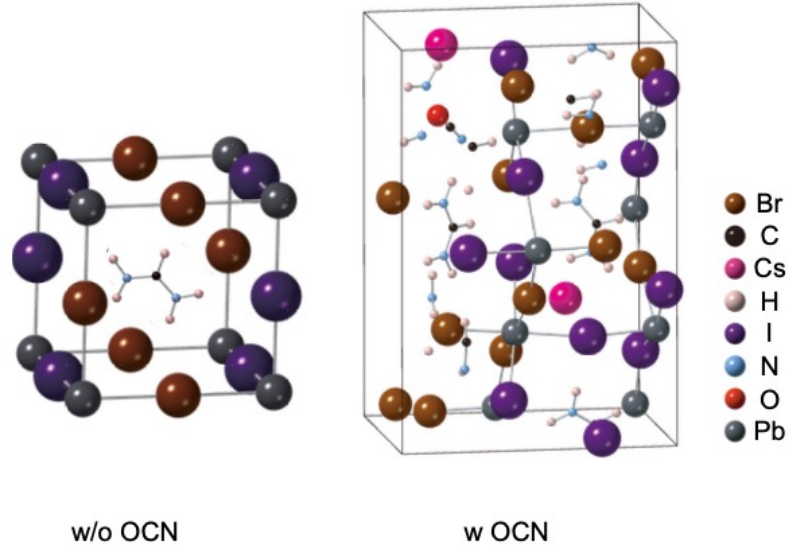
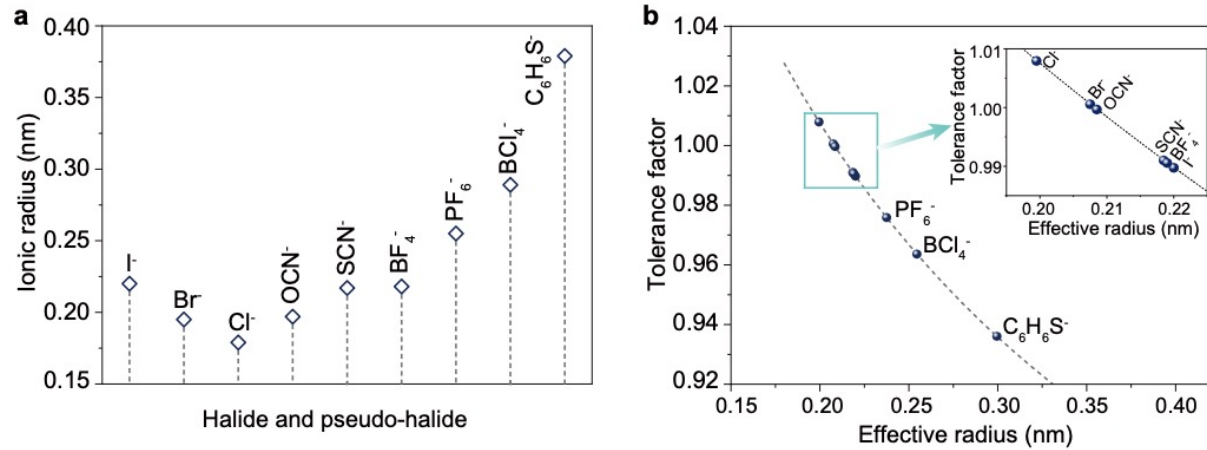
Triple-junction perovskite/perovskite/Si



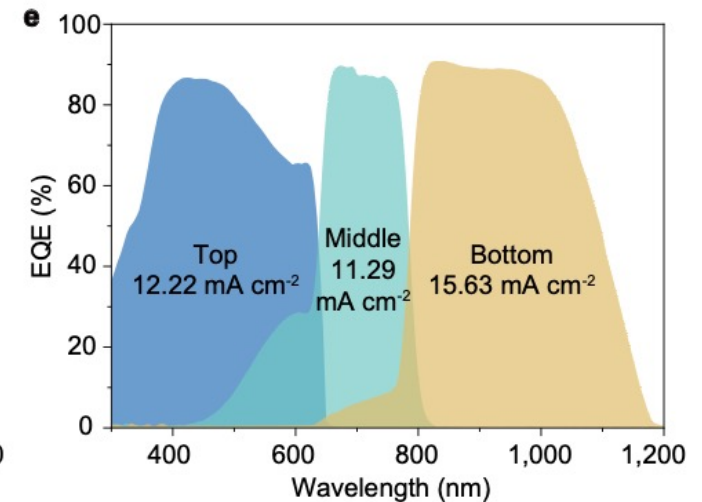
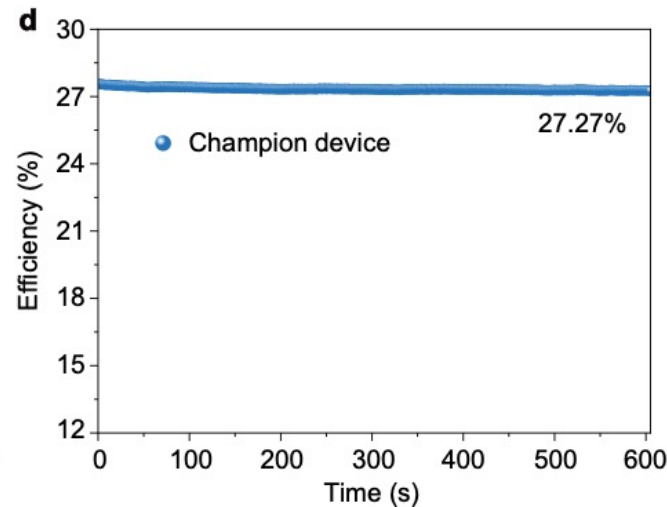
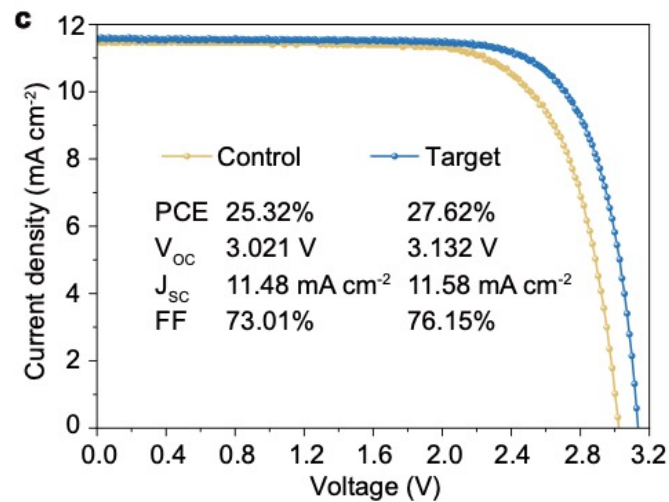
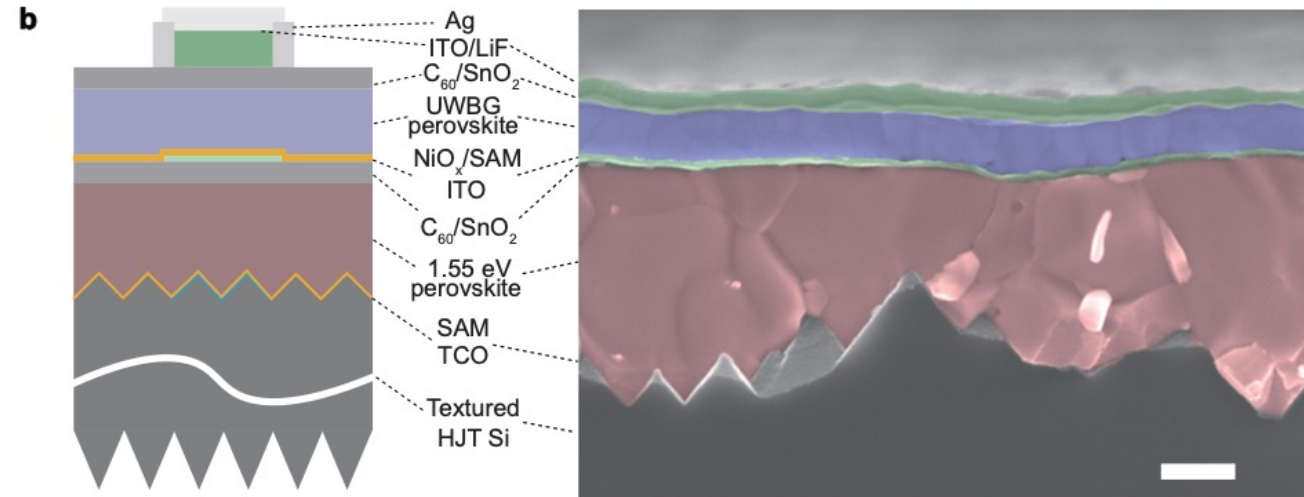
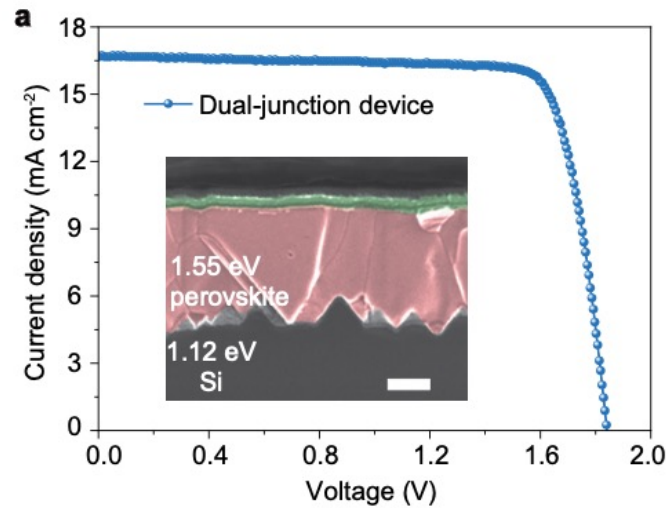
Perovskite/Si (1.7eV/1.1eV)

Perovskite/Perovskite/Si (1.9eV/1.5eV/1.1eV)

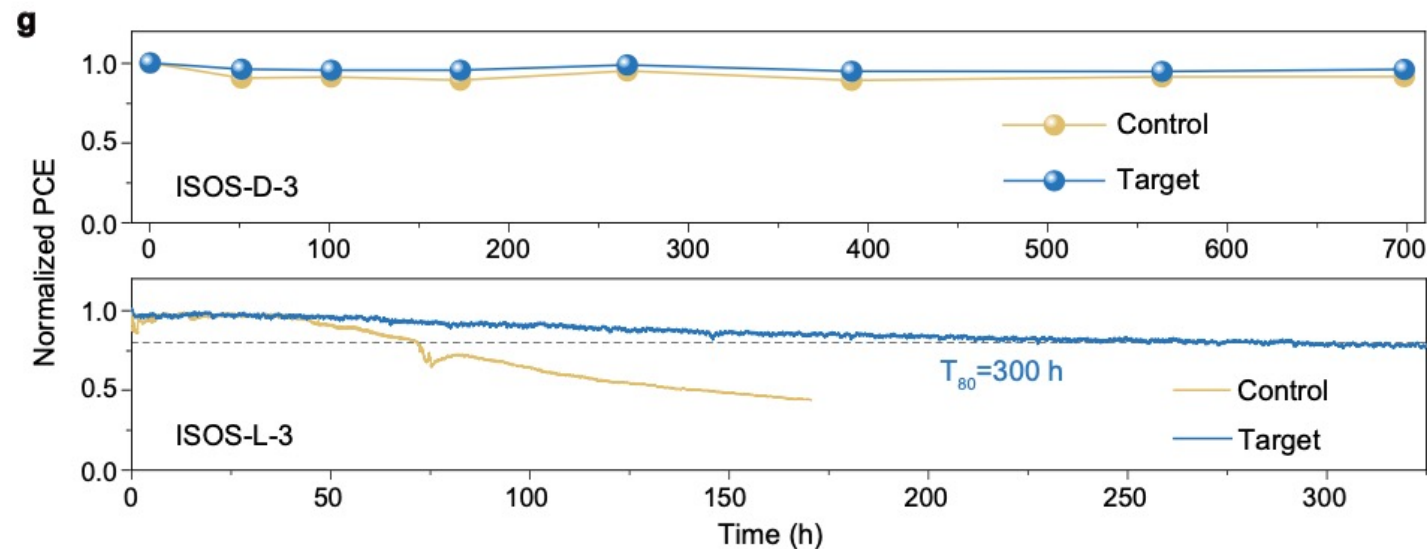
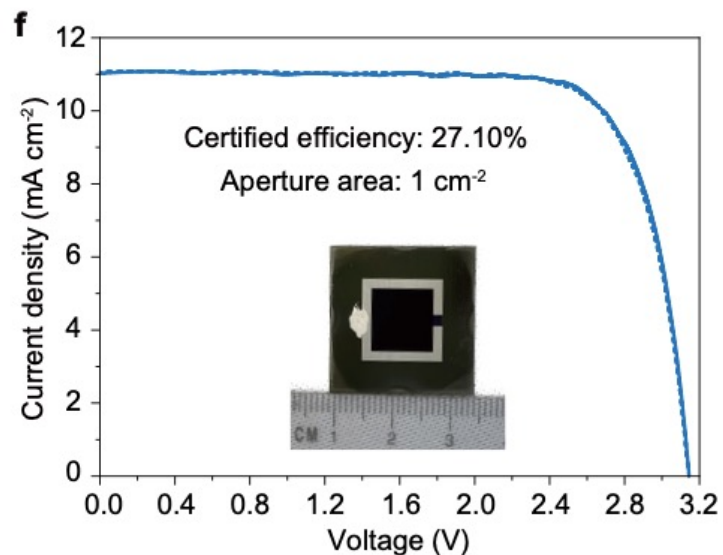
Triple-junction perovskite/perovskite/Si



Triple-junction perovskite/perovskite/Si



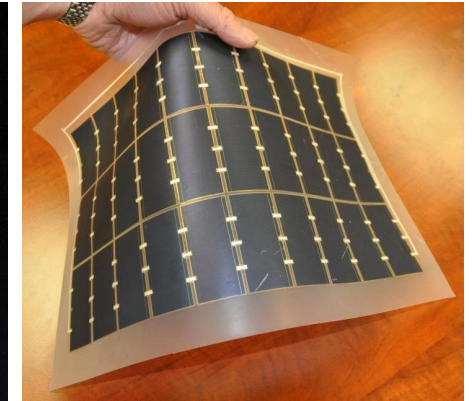
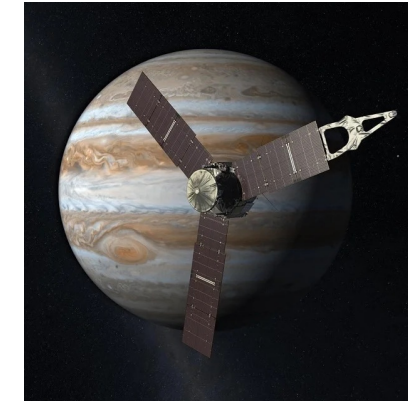
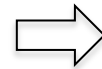
Triple-junction perovskite/perovskite/Si



Centralized and decentralized PV

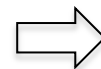
- from *PK/Si* to *PK-based thin-film tandems*

❑ III–V tandem (PCE = 30%)



❑ Organic tandem (PCE = 10%)

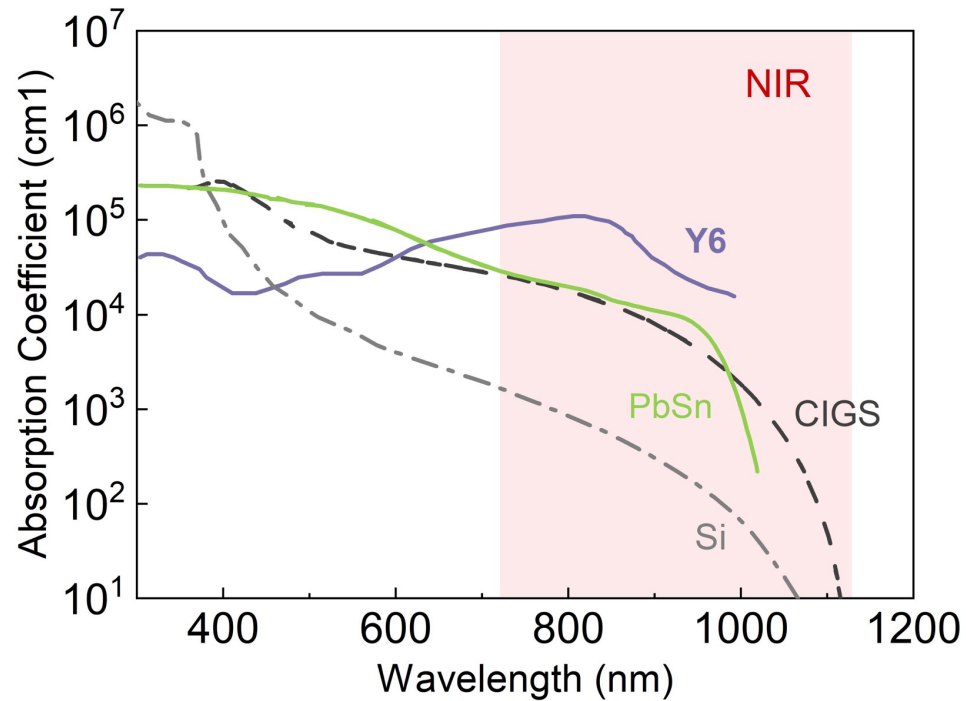
- ❑ Lightweight;
- ❑ Aesthetics;
- ❑ Efficient (>30%);
- ❑ Lifetime (~10 years)



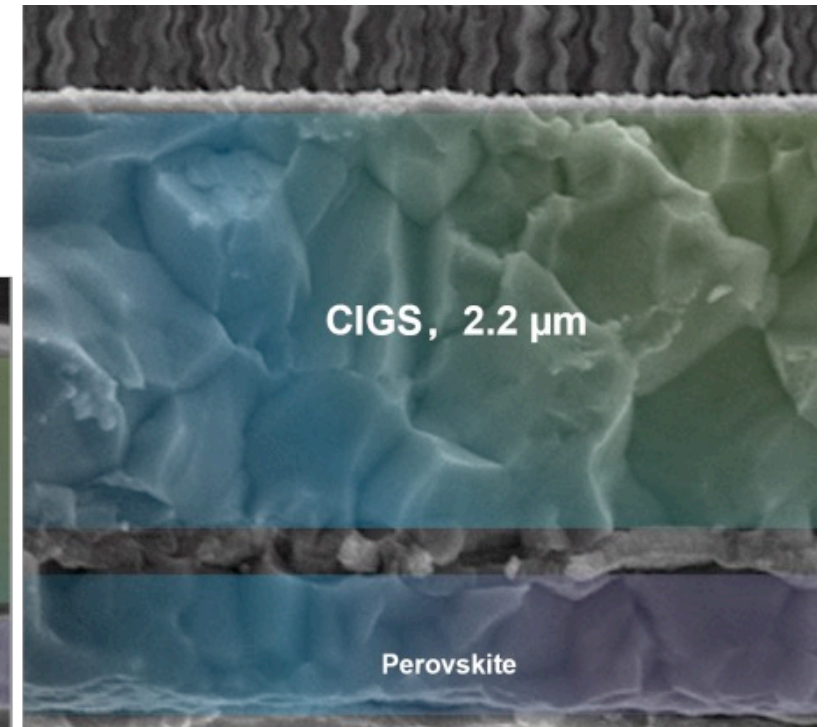
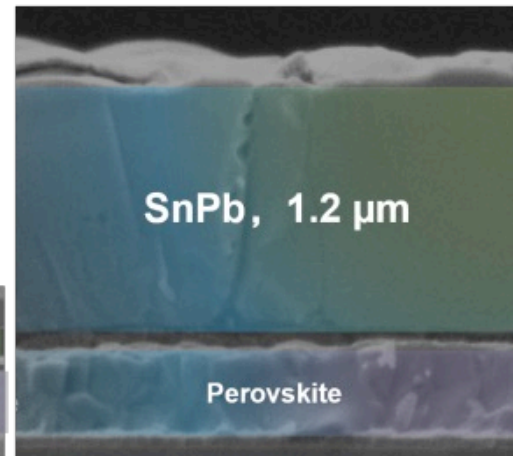
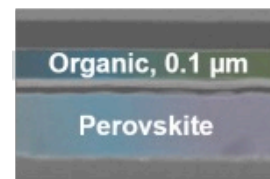
Thin-film-based tandem
(PCE = 30%)



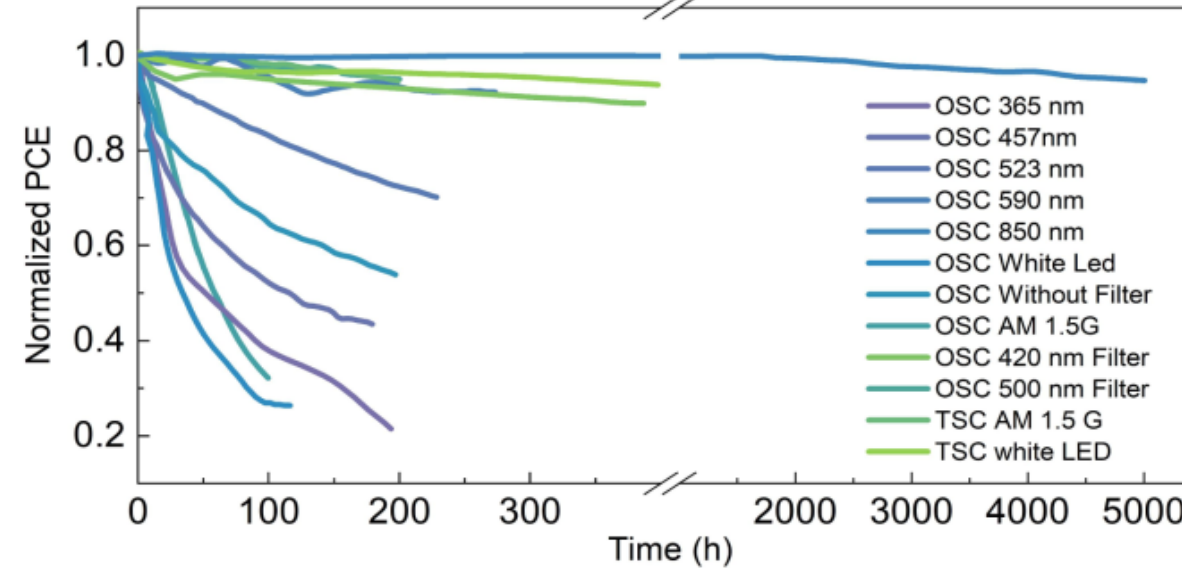
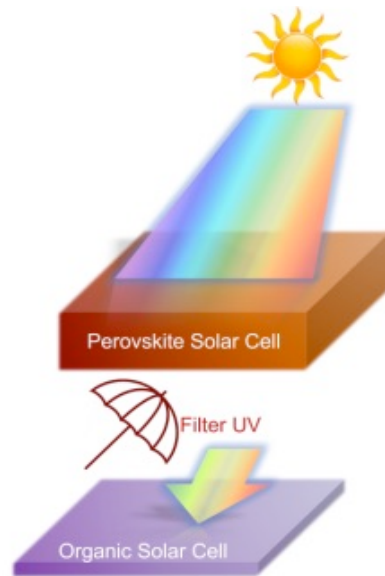
Integrating with other established thin-film PV technologies



□ Organic materials are effective near-infrared (NIR) absorbers

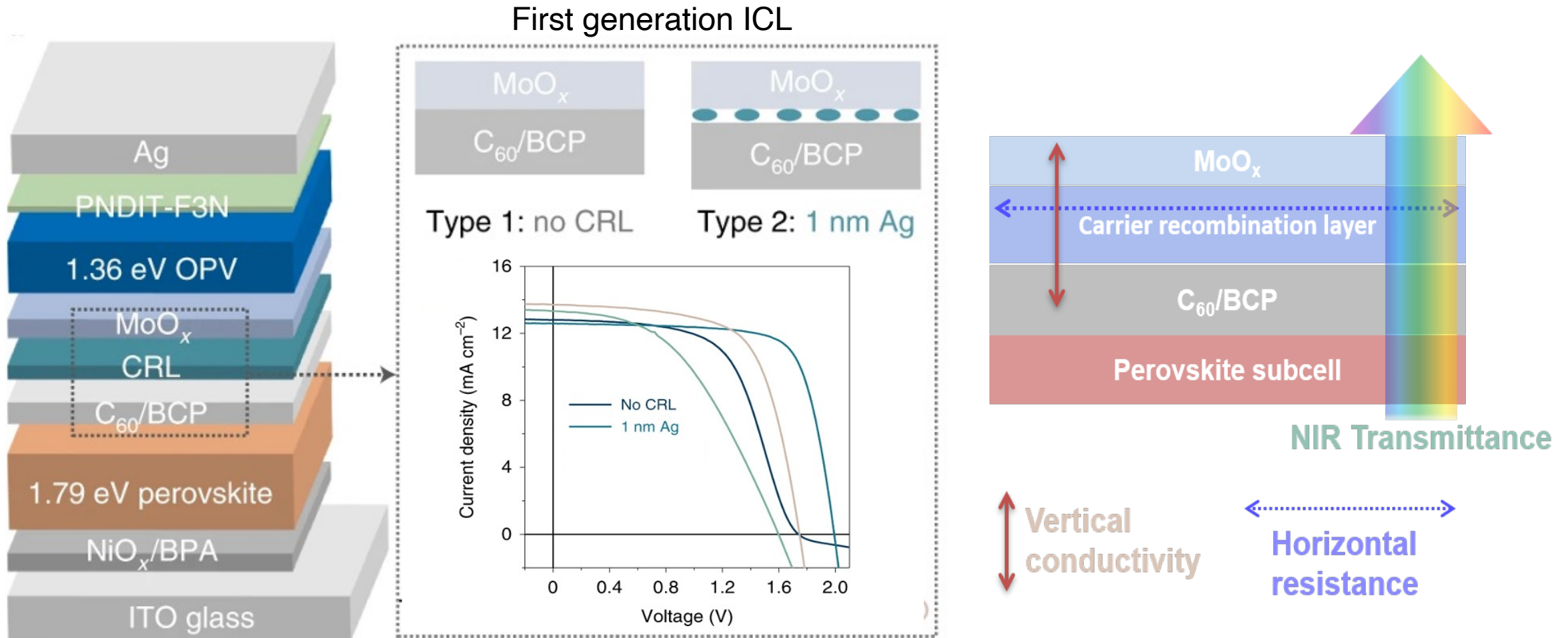


OPV becoming more stable in tandem configuration



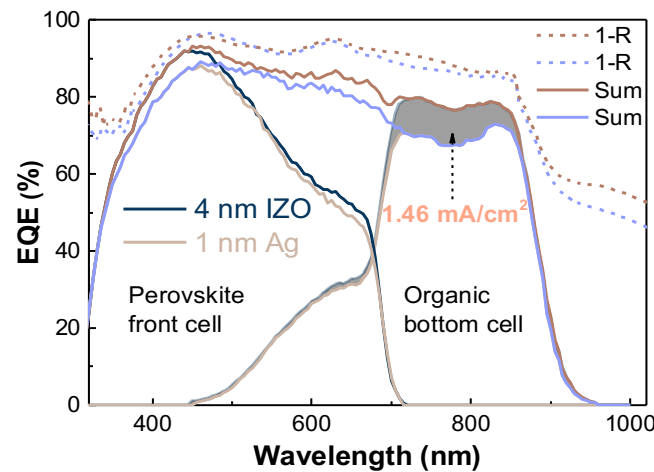
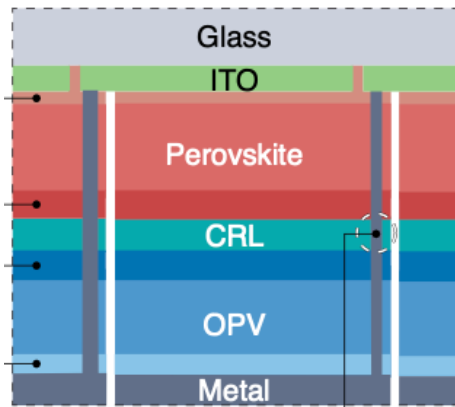
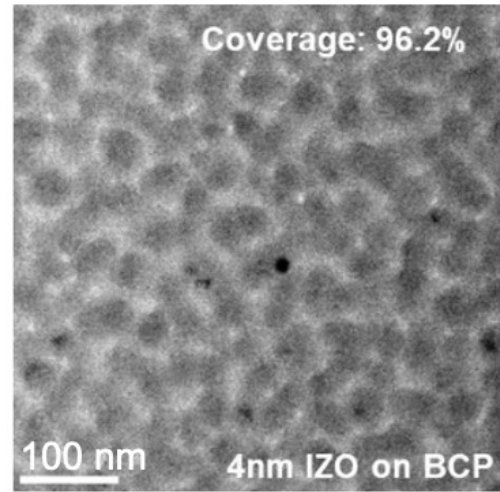
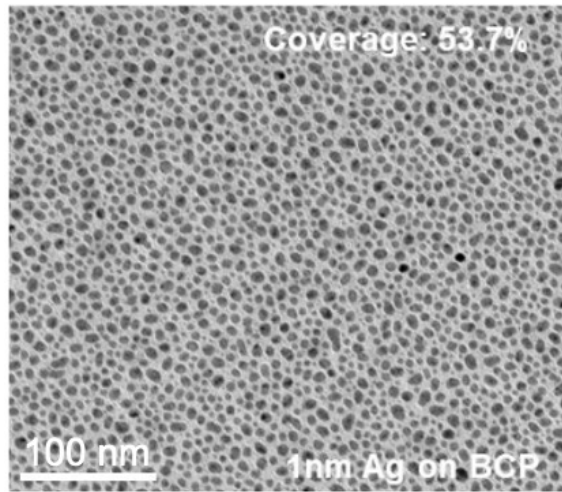
- ❑ Perovskite block all the high energy photons
- ❑ Organic materials are relatively stable under near-infrared light

First generation interconnecting layer (ICL)'s issues

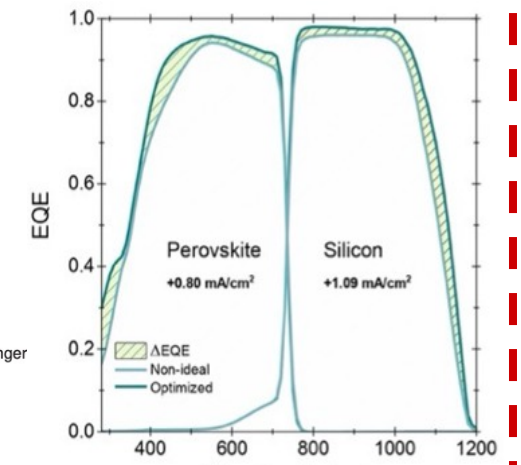
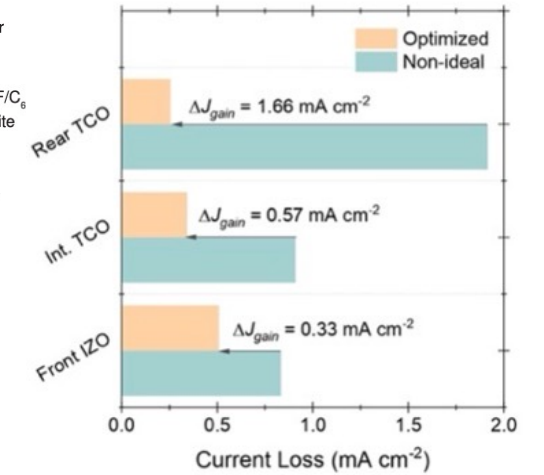
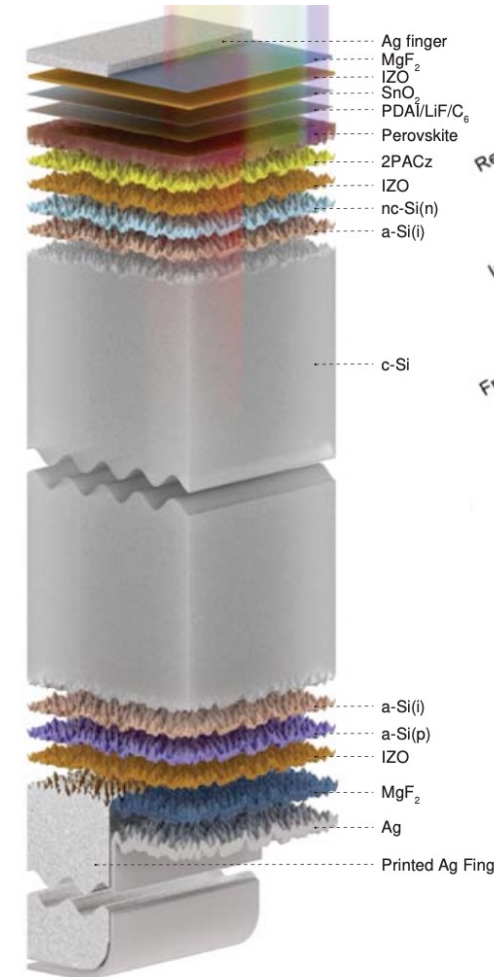


Second generation ICL – Ultrathin TCOs

Perovskite/Organics



Perovskite/Si



Certified record efficient perovskite/organic tandem

Received: 12 May 2022 | Revised: 23 May 2022 | Accepted: 25 May 2022

DOI: 10.1002/pip.3595

SHORT COMMUNICATION

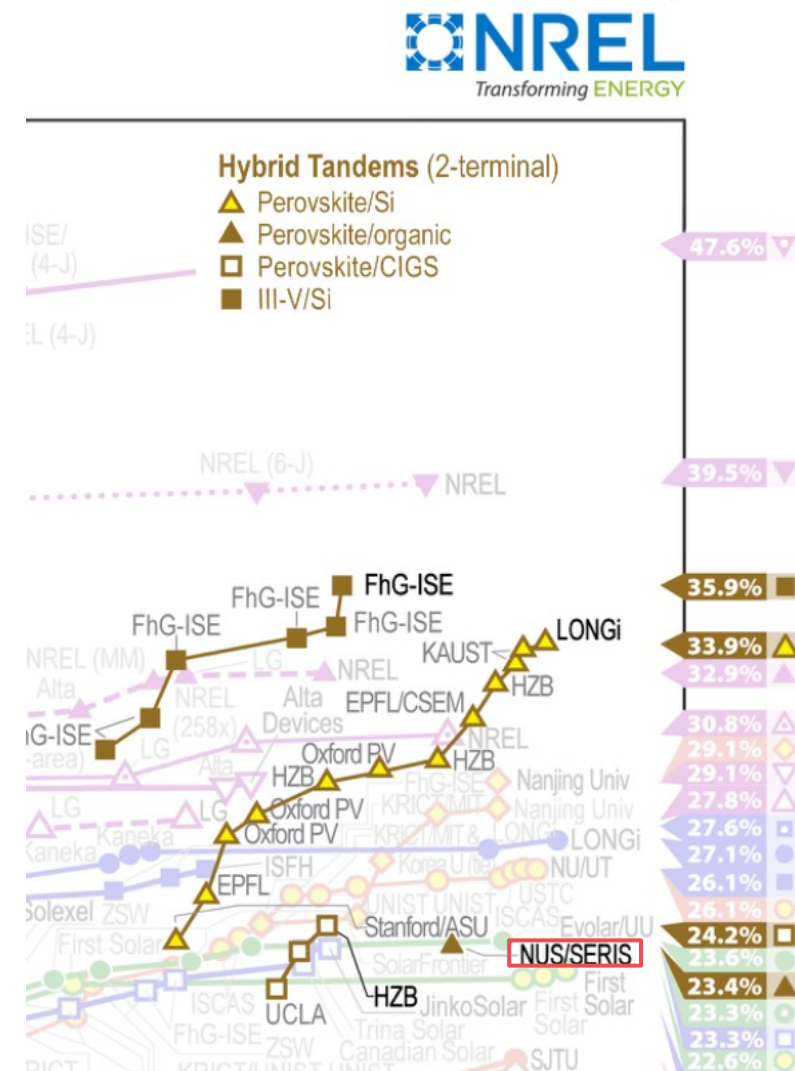


Solar cell efficiency tables (Version 60)

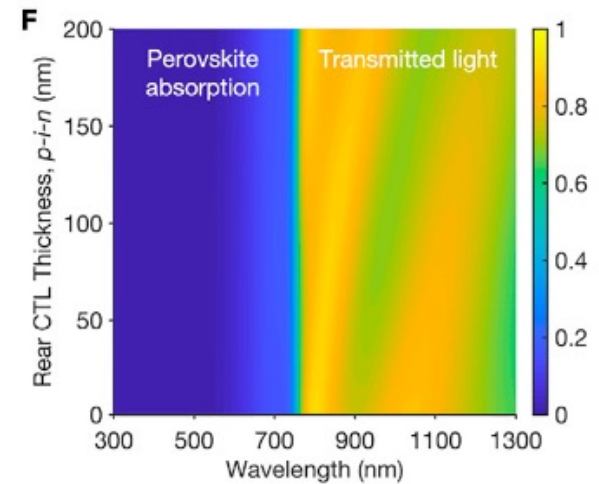
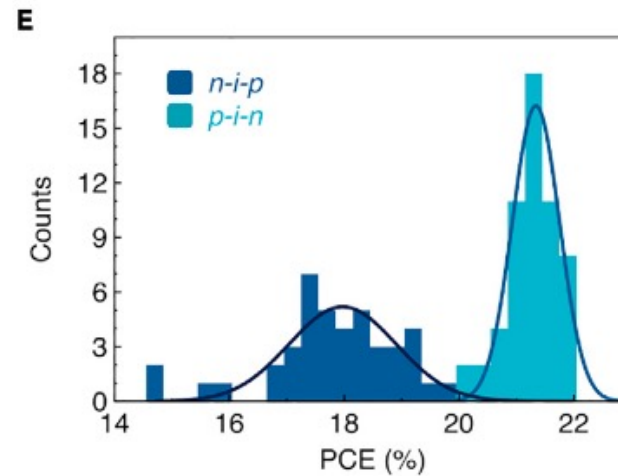
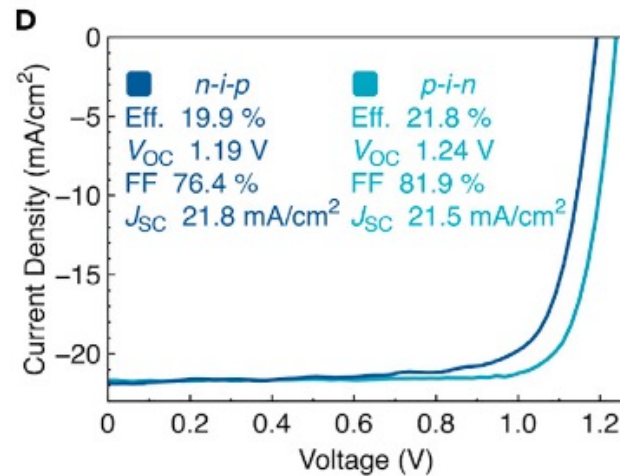
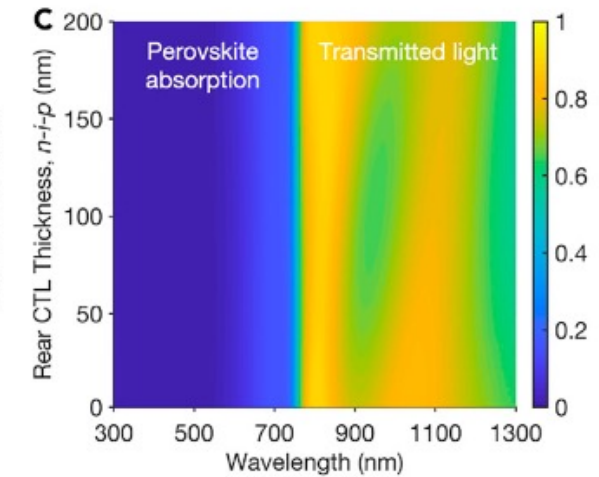
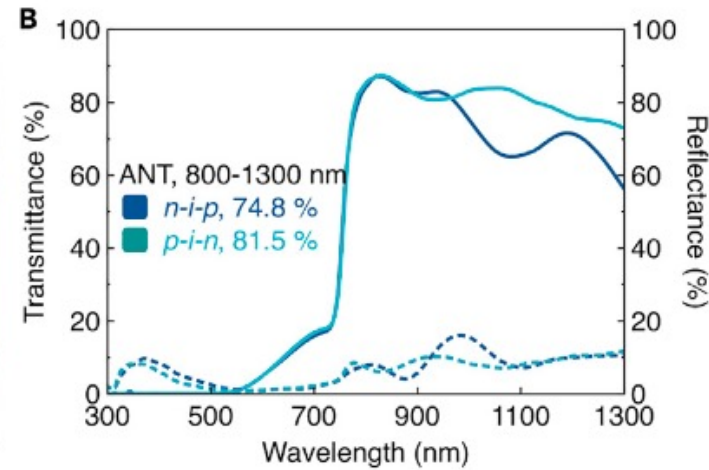
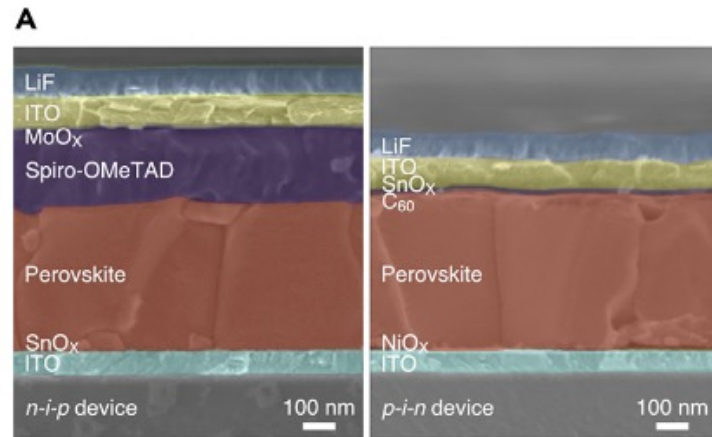
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 Masahiro Yoshita⁴ | Nikos Kopidakis⁵ | Karsten Bothe⁶ | David Hinken⁶ |
 Michael Rauer³ | Xiaojing Hao¹

TABLE 3 (Continued)

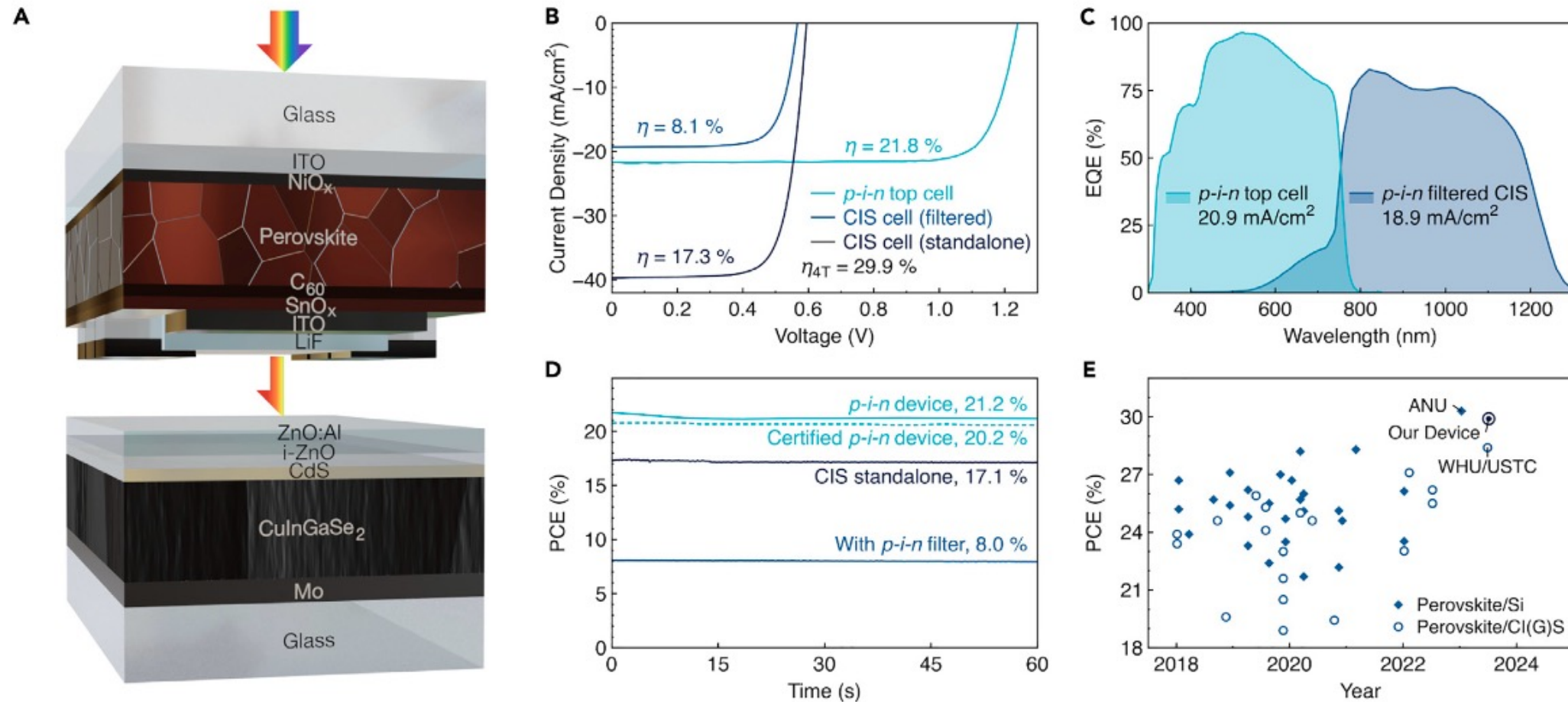
Classification	Efficiency (%)	Area (cm ²)	V _{oc} (V)	J _{sc} (mA/cm ²)	Fill factor (%)	Test centre (date)	Description
Perovskite/organic	23.4 ± 0.8 ^h	0.0552 (da)	2.136	14.56 ⁱ	75.6	JET (3/22)	NUS/SERIS, 2-term. ⁵⁴



NIR light management by controlling interference spectrum



Performance of the perovskite/CIS tandem solar cell



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SINGAPORE

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